

# TLV2332, TLV2332Y, TLV2334, TLV2334Y LinCMOS™ LOW-VOLTAGE MEDIUM-POWER OPERATIONAL AMPLIFIERS

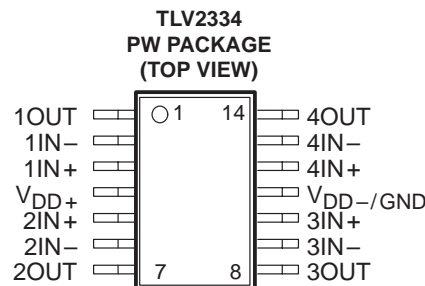
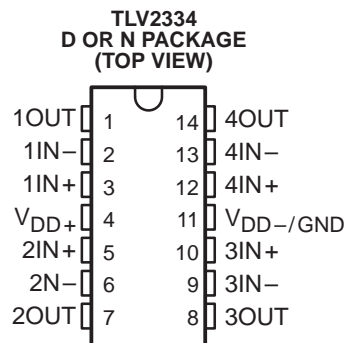
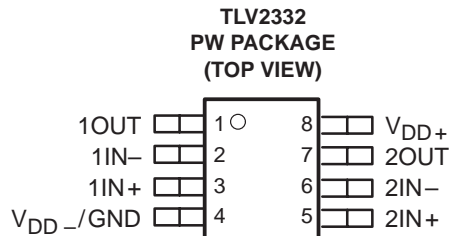
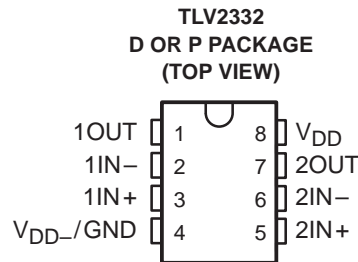
SLOS189 – FEBRUARY 1997

- **Wide Range of Supply Voltages Over Specified Temperature Range:**  
 $T_A = -40^\circ\text{C to } 85^\circ\text{C} \dots 2\text{ V to } 8\text{ V}$
- **Fully Characterized at 3 V and 5 V**
- **Single-Supply Operation**
- **Common-Mode Input-Voltage Range Extends Below the Negative Rail and up to  $V_{DD} - 1\text{ V}$  at  $T_A = 25^\circ\text{C}$**
- **Output Voltage Range Includes Negative Rail**
- **High Input Impedance . . .  $10^{12}\ \Omega$  Typ**
- **ESD-Protection Circuitry**
- **Designed-In Latch-Up Immunity**

## description

The TLV233x operational amplifiers are in a family of devices that has been specifically designed for use in low-voltage single-supply applications. Unlike the TLV2322 which is optimized for ultra-low power, the TLV233x is designed to provide a combination of low power and good ac performance. Each amplifier is fully functional down to a minimum supply voltage of 2 V, is fully characterized, tested, and specified at both 3-V and 5-V power supplies. The common-mode input-voltage range includes the negative rail and extends to within 1 V of the positive rail.

Having a maximum supply current of only 310  $\mu\text{A}$  per amplifier over full temperature range, the TLV233x devices offer a combination of good ac performance and microampere supply currents. From a 3-V power supply, the amplifier's typical slew rate is 0.38 V/ $\mu\text{s}$  and its bandwidth is 300 kHz.



## AVAILABLE OPTIONS

T <sub>A</sub>	V <sub>IO</sub> max AT 25°C	PACKAGED DEVICES				CHIP FORMS <sup>§</sup> (Y)
		SMALL OUTLINE† (D)	PLASTIC DIP (N)	PLASTIC DIP (P)	TSSOP‡ (PW)	
-40°C to 85°C	9 mV	TLV2332ID	—	TLV2332IP	TLV2332IPWLE	TLV2332Y
	10 mV	TLV2334ID	TLV2334IN	—	TLV2334IPWLE	TLV2334Y

† The D package is available taped and reeled. Add R suffix to the device type (e.g., TLV2332IDR).

‡ The PW package is only available left-end taped and reeled (e.g., TLV2332IPWLE).

§ Chip forms are tested at 25°C only.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

LinCMOS is a trademark of Texas Instruments Incorporated.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

**TEXAS  
INSTRUMENTS**

POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Copyright © 1997, Texas Instruments Incorporated

# TLV2332, TLV2332Y, TLV2334, TLV2334Y LinCMOS™ LOW-VOLTAGE MEDIUM-POWER OPERATIONAL AMPLIFIERS

SLOS189 – FEBRUARY 1997

## description (continued)

These amplifiers offer a level of ac performance greater than that of many other devices operating at comparable power levels. The TLV233x operational amplifiers are especially well suited for use in low-current or battery-powered applications.

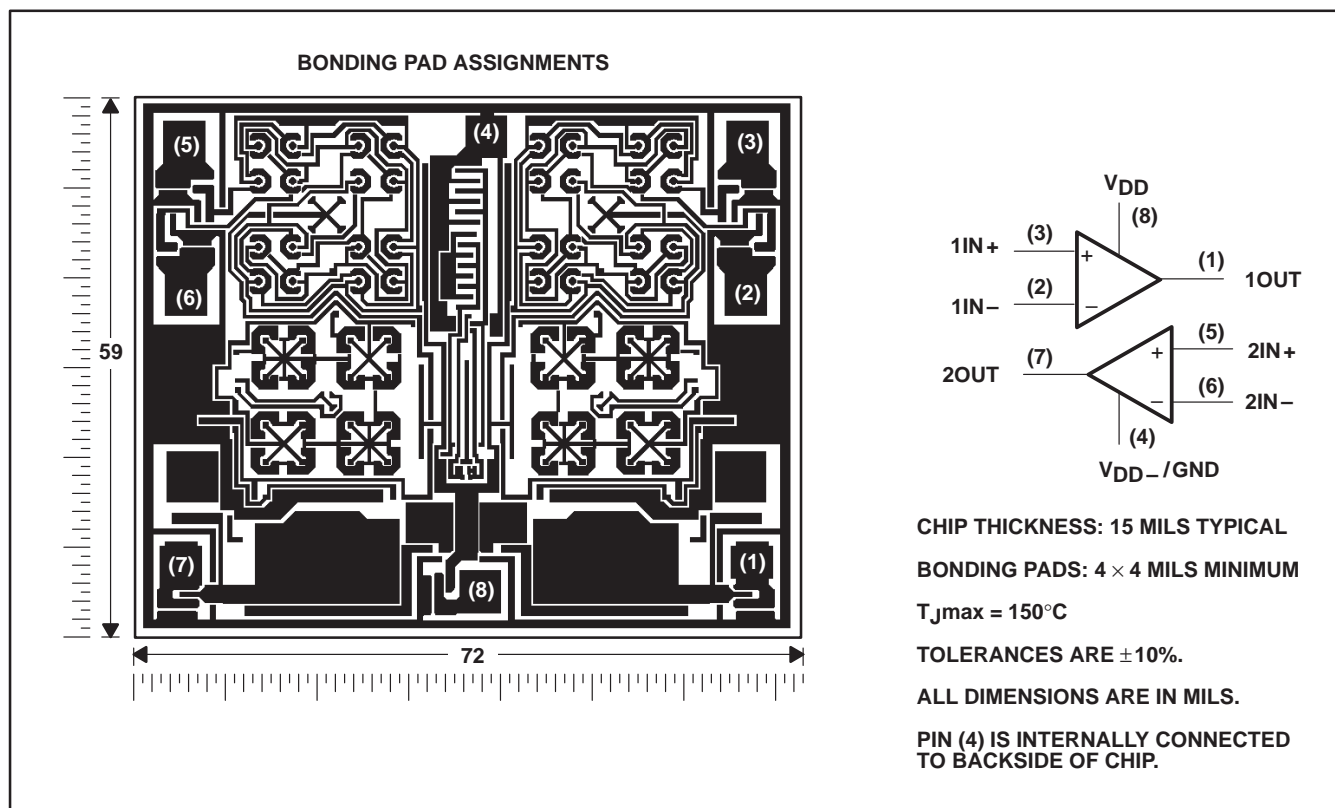
Low-voltage and low-power operation has been made possible by using the Texas Instruments silicon-gate LinCMOS™ technology. The LinCMOS process also features extremely high input impedance and ultra-low bias currents making these amplifiers ideal for interfacing to high-impedance sources such as sensor circuits or filter applications.

To facilitate the design of small portable equipment, the TLV233x is made available in a wide range of package options, including the small-outline and thin-shrink small-outline package (TSSOP). The TSSOP package has significantly reduced dimensions compared to a standard surface-mount package. Its maximum height of only 1.1 mm makes it particularly attractive when space is critical.

The device inputs and outputs are designed to withstand –100-mA currents without sustaining latch-up. The TLV233x incorporates internal ESD-protection circuits that prevents functional failures at voltages up to 2000 V as tested under MIL-STD 883C, Method 3015.2; however, care should be exercised in handling these devices as exposure to ESD may result in the degradation of the device parametric performance.

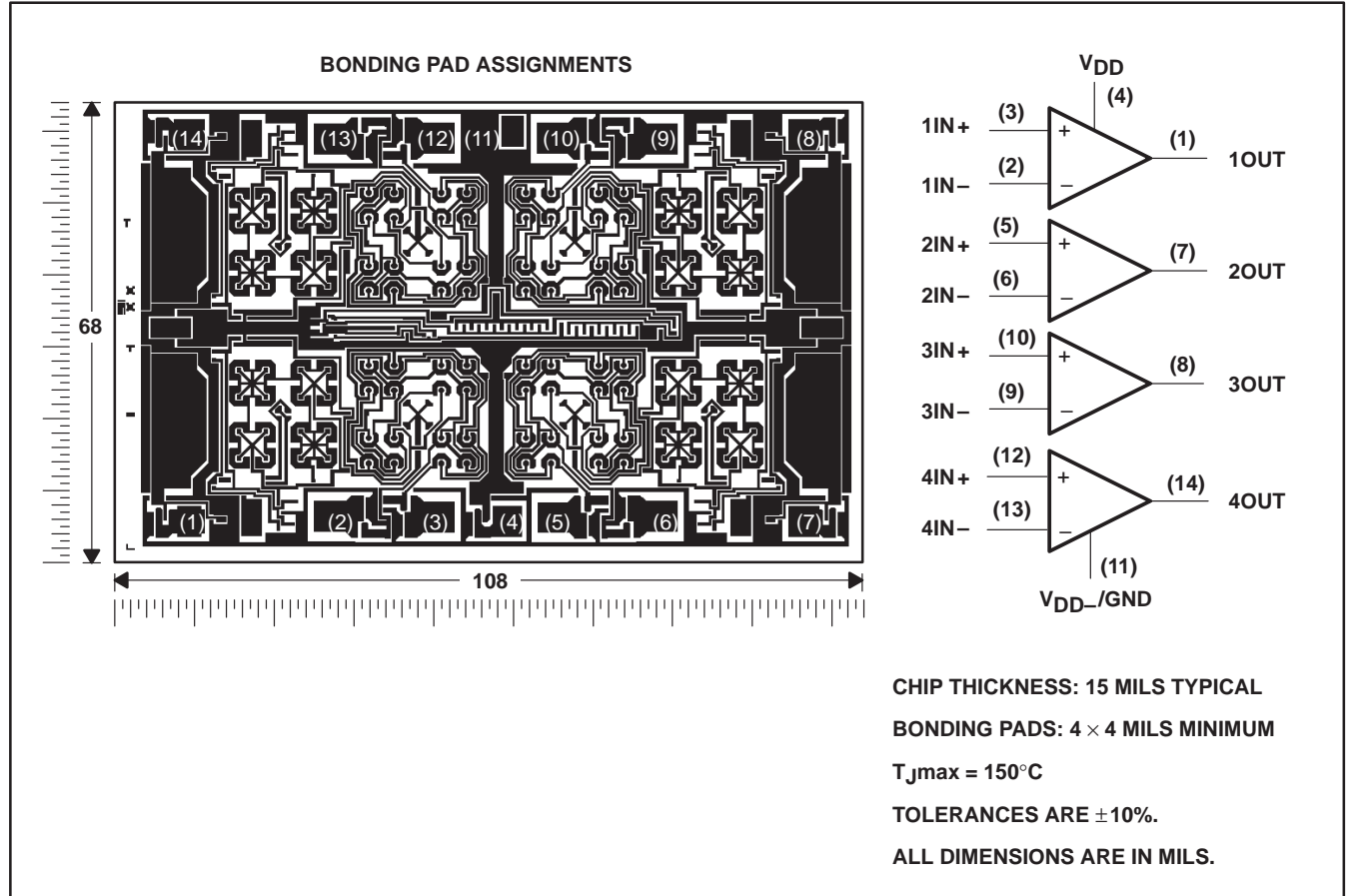
## TLV2332Y chip information

This chip, when properly assembled, display characteristics similar to the TLV2332. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



### TLV2334Y chip information

This chip, when properly assembled, displays characteristics similar to the TLV2334. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.

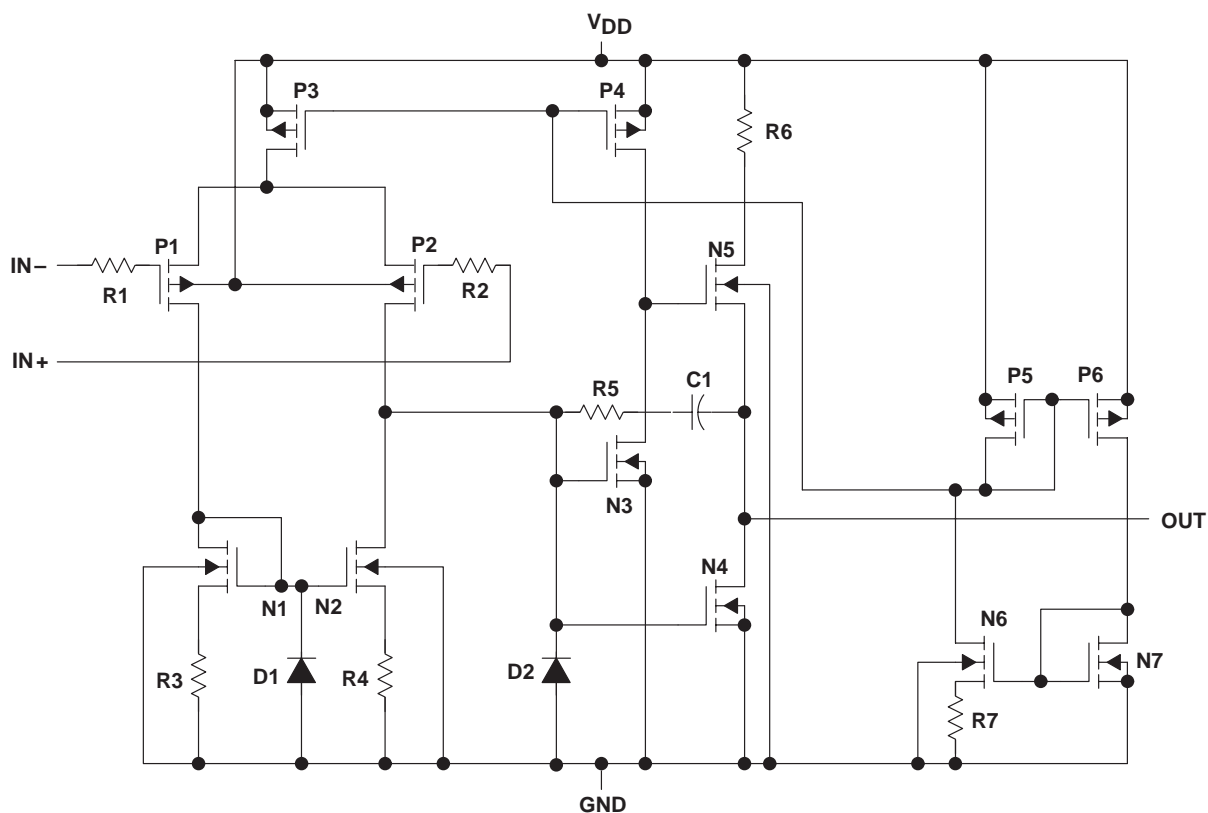


# TLV2332, TLV2332Y, TLV2334, TLV2334Y

## LinCMOS™ LOW-VOLTAGE MEDIUM-POWER OPERATIONAL AMPLIFIERS

SLOS189 – FEBRUARY 1997

### equivalent schematic (each amplifier)



ACTUAL DEVICE COMPONENT COUNT†		
COMPONENT	TLV2332	TLV2334
Transistors	54	108
Resistors	14	28
Diodes	4	8
Capacitors	2	4

† Includes both amplifiers and all ESD, bias, and trim circuitry.

**absolute maximum ratings over operating free-air temperature (unless otherwise noted)†**

Supply voltage, $V_{DD}$ (see Note 1)	8 V
Differential input voltage, $V_{ID}$ (see Note 2)	$V_{DD} \pm$
Input voltage range, $V_I$ (any input)	–0.3 V to $V_{DD}$
Input current, $I_I$	$\pm 5$ mA
Output current, $I_O$	$\pm 30$ mA
Duration of short-circuit current at (or below) $T_A = 25^\circ\text{C}$ (see Note 3)	unlimited
Continuous total dissipation	See Dissipation Rating Table
Operating free-air temperature range, $T_A$	–40°C to 85°C
Storage temperature range	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES:
1. All voltage values, except differential voltages, are with respect to network ground.
  2. Differential voltages are at the noninverting input with respect to the inverting input.
  3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded (see application section).

**DISSIPATION RATING TABLE**

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 85^\circ\text{C}$ POWER RATING
D–8	725 mW	5.8 mW/°C	377 mW
D–14	950 mW	7.6 mW/°C	494 mW
N	1575 mW	12.6 mW/°C	819 mW
P	1000 mW	8.0 mW/°C	520 mW
PW–8	525 mW	4.2 mW/°C	273 mW
PW–14	700 mW	5.6 mW/°C	364 mW

**recommended operating conditions**

		MIN	MAX	UNIT
Supply voltage, $V_{DD}$		2	8	V
Common-mode input voltage, $V_{IC}$	$V_{DD} = 3$ V	–0.2	1.8	V
	$V_{DD} = 5$ V	–0.2	3.8	
Operating free-air temperature, $T_A$		–40	85	°C

**TLV2332, TLV2332Y, TLV2334, TLV2334Y**  
**LinCMOS™ LOW-VOLTAGE MEDIUM-POWER**  
**OPERATIONAL AMPLIFIERS**

SLOS189 – FEBRUARY 1997

**TLV2332I electrical characteristics at specified free-air temperature**

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TLV2332I						UNIT
			V <sub>DD</sub> = 3 V			V <sub>DD</sub> = 5 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
V <sub>IO</sub> Input offset voltage	V <sub>O</sub> = 1 V, V <sub>IC</sub> = 1 V, R <sub>S</sub> = 50 Ω, R <sub>L</sub> = 100 kΩ	25°C	0.6		9	1.1		9	mV
		Full range	11			11			
α <sub>VIO</sub> Average temperature coefficient of input offset voltage		25°C to 85°C	1			1.7			μV/°C
I <sub>IO</sub> Input offset current (see Note 4)	V <sub>O</sub> = 1 V, V <sub>IC</sub> = 1 V	25°C	0.1		0.1				pA
		85°C	22	1000	24	1000			
I <sub>IB</sub> Input bias current (see Note 4)	V <sub>O</sub> = 1 V, V <sub>IC</sub> = 1 V	25°C	0.6		0.6				pA
		85°C	175	2000	200	2000			
V <sub>ICR</sub> Common-mode input voltage range (see Note 5)		25°C	-0.2 to 2	-0.3 to 2.3	-0.2 to 4		-0.3 to 4.2		V
		Full range	-0.2 to 1.8		-0.2 to 3.8				
V <sub>OH</sub> High-level output voltage	V <sub>IC</sub> = 1 V, V <sub>ID</sub> = 100 mV, I <sub>OH</sub> = -1 mA	25°C	1.75	1.9	3.2	3.9			V
		Full range	1.7		3				
V <sub>OL</sub> Low-level output voltage	V <sub>IC</sub> = 1 V, V <sub>ID</sub> = -100 mV, I <sub>OL</sub> = 1 mA	25°C	115		150	95		150	mV
		Full range	190			190			
A <sub>VD</sub> Large-signal differential voltage amplification	V <sub>IC</sub> = 1 V, R <sub>L</sub> = 100 kΩ, See Note 6	25°C	25	83	25	170			V/mV
		Full range	15		15				
CMRR Common-mode rejection ratio	V <sub>O</sub> = 1 V, V <sub>IC</sub> = V <sub>ICRmin</sub> , R <sub>S</sub> = 50 Ω	25°C	65	92	65	91			dB
		Full range	60		60				
k <sub>SVR</sub> Supply-voltage rejection ratio (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	V <sub>IC</sub> = 1 V, V <sub>O</sub> = 1 V, R <sub>S</sub> = 50 Ω	25°C	70	94	70	94			dB
		Full range	65		65				
I <sub>DD</sub> Supply current	V <sub>O</sub> = 1 V, V <sub>IC</sub> = 1 V, No load	25°C	160		500	210		560	μA
		Full range	620			800			

† Full range is -40°C to 85°C.

- NOTES: 4. The typical values of input bias current and input offset current below 5 pA are determined mathematically.  
5. This range also applies to each input individually.  
6. At V<sub>DD</sub> = 5 V, V<sub>O</sub> = 0.25 V to 2 V; at V<sub>DD</sub> = 3 V, V<sub>O</sub> = 0.5 V to 1.5 V.



TLV2332, TLV2332Y, TLV2334, TLV2334Y  
**LinCMOS™ LOW-VOLTAGE MEDIUM-POWER  
 OPERATIONAL AMPLIFIERS**

SLOS189 – FEBRUARY 1997

**TLV2332I operating characteristics at specified free-air temperature,  $V_{DD} = 3\text{ V}$**

PARAMETER	TEST CONDITIONS	$T_A$	TLV2332I			UNIT
			MIN	TYP	MAX	
SR      Slew rate at unity gain	$V_{IC} = 1\text{ V}$ , $R_L = 100\text{ k}\Omega$ , See Figure 34	$V_{I(PP)} = 1\text{ V}$ , $C_L = 20\text{ pF}$ ,	25°C	0.38		V/ $\mu$ s
			85°C	0.29		
$V_n$ Equivalent input noise voltage	$f = 1\text{ kHz}$ , See Figure 35	$R_S = 20\ \Omega$ ,	25°C	32		nV/ $\sqrt{\text{Hz}}$
$B_{OM}$ Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_L = 100\text{ k}\Omega$ ,	$C_L = 20\text{ pF}$ , See Figure 34	25°C	34		kHz
			85°C	32		
$B_1$ Unity-gain bandwidth	$V_I = 10\text{ mV}$ , $R_L = 100\text{ k}\Omega$ ,	$C_L = 20\text{ pF}$ , See Figure 36	25°C	300		kHz
			85°C	235		
$\phi_m$ Phase margin	$V_I = 10\text{ mV}$ , $C_L = 20\text{ pF}$ , See Figure 36	$f = B_1$ , $R_L = 100\text{ k}\Omega$ ,	-40°C	42°		
			25°C	39°		
			85°C	36°		

**TLV2332I operating characteristics at specified free-air temperature,  $V_{DD} = 5\text{ V}$**

PARAMETER	TEST CONDITIONS	$T_A$	TLV2332I			UNIT
			MIN	TYP	MAX	
SR      Slew rate at unity gain	$V_{IC} = 1\text{ V}$ , $R_L = 100\text{ k}\Omega$ , $C_L = 20\text{ pF}$ , See Figure 34	$V_{I(PP)} = 1\text{ V}$	25°C	0.43		V/ $\mu$ s
			85°C	0.35		
		$V_{I(PP)} = 2.5\text{ V}$	25°C	0.40		
			85°C	0.32		
$V_n$ Equivalent input noise voltage	$f = 1\text{ kHz}$ , See Figure 35	$R_S = 20\ \Omega$ ,	25°C	32		nV/ $\sqrt{\text{Hz}}$
$B_{OM}$ Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_L = 100\text{ k}\Omega$ ,	$C_L = 20\text{ pF}$ , See Figure 34	25°C	55		kHz
			85°C	45		
$B_1$ Unity-gain bandwidth	$V_I = 10\text{ mV}$ , $R_L = 100\text{ k}\Omega$ ,	$C_L = 20\text{ pF}$ , See Figure 36	25°C	525		kHz
			85°C	370		
$\phi_m$ Phase margin	$V_I = 10\text{ mV}$ , $C_L = 20\text{ pF}$ , See Figure 36	$f = B_1$ , $R_L = 100\text{ k}\Omega$ ,	-40°C	43°		
			25°C	40°		
			85°C	38°		

**TLV2332, TLV2332Y, TLV2334, TLV2334Y**  
**LinCMOS™ LOW-VOLTAGE MEDIUM-POWER**  
**OPERATIONAL AMPLIFIERS**

SLOS189 – FEBRUARY 1997

**TLV2334I electrical characteristics at specified free-air temperature**

PARAMETER	TEST CONDITIONS	T <sub>A</sub> †	TLV2334I						UNIT
			V <sub>DD</sub> = 3 V			V <sub>DD</sub> = 5 V			
			MIN	TYP	MAX	MIN	TYP	MAX	
V <sub>IO</sub> Input offset voltage	V <sub>O</sub> = 1 V, V <sub>IC</sub> = 1 V, R <sub>S</sub> = 50 Ω, R <sub>L</sub> = 100 kΩ	25°C	0.6		10	1.1		10	mV
		Full range	12			12			
α <sub>VIO</sub> Average temperature coefficient of input offset voltage		25°C to 85°C	1			1.7			μV/°C
I <sub>IO</sub> Input offset current (see Note 4)	V <sub>O</sub> = 1 V, V <sub>IC</sub> = 1 V	25°C	0.1			0.1			pA
		85°C	22	1000		24	1000		
I <sub>IB</sub> Input bias current (see Note 4)	V <sub>O</sub> = 1 V, V <sub>IC</sub> = 1 V	25°C	0.6			0.6			pA
		85°C	175	2000		200	2000		
V <sub>ICR</sub> Common-mode input voltage range (see Note 5)		25°C	-0.2 to 2	-0.3 to 2.3		-0.2 to 4	-0.3 to 4.2		V
		Full range	-0.2 to 1.8			-0.2 to 3.8			V
V <sub>OH</sub> High-level output voltage	V <sub>IC</sub> = 1 V, V <sub>ID</sub> = 100 mV, I <sub>OH</sub> = -1 mA	25°C	1.75	1.9		3.2	3.9		V
		Full range	1.7			3			
V <sub>OL</sub> Low-level output voltage	V <sub>IC</sub> = 1 V, V <sub>ID</sub> = -100 mV, I <sub>OL</sub> = 1 mA	25°C	115		150	95		150	mV
		Full range	190			190			
A <sub>VD</sub> Large-signal differential voltage amplification	V <sub>IC</sub> = 1 V, R <sub>L</sub> = 100 kΩ, See Note 6	25°C	25	83		25	170		V/mV
		Full range	15			15			
CMRR Common-mode rejection ratio	V <sub>O</sub> = 1 V, V <sub>IC</sub> = V <sub>ICRmin</sub> , R <sub>S</sub> = 50 Ω	25°C	65	92		65	91		dB
		Full range	60			60			
k <sub>SVR</sub> Supply-voltage rejection ratio (ΔV <sub>DD</sub> /ΔV <sub>IO</sub> )	V <sub>DD</sub> = 3 V to 5 V, V <sub>IC</sub> = 1 V, V <sub>O</sub> = 1 V, R <sub>S</sub> = 50 Ω	25°C	70	94		70	94		dB
		Full range	65			65			
I <sub>DD</sub> Supply current	V <sub>O</sub> = 1 V, V <sub>IC</sub> = 1 V, No load	25°C	320		1000	420		1120	μA
		Full range	1200			1600			

† Full range is -40°C to 85°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA are determined mathematically.

5. This range also applies to each input individually.

6. At V<sub>DD</sub> = 5 V, V<sub>O</sub> = 0.25 V to 2 V; at V<sub>DD</sub> = 3 V, V<sub>O</sub> = 0.5 V to 1.5 V.





**TLV2334I operating characteristics at specified free-air temperature,  $V_{DD} = 3\text{ V}$**

PARAMETER	TEST CONDITIONS	$T_A$	TLV2334I			UNIT
			MIN	TYP	MAX	
SR Slew rate at unity gain	$V_{IC} = 1\text{ V}$ , $R_L = 100\text{ k}\Omega$ , See Figure 34	$V_{I(PP)} = 1\text{ V}$ , $C_L = 20\text{ pF}$	25°C	0.38		V/ $\mu$ s
			85°C	0.29		
$V_n$ Equivalent input noise voltage	$f = 1\text{ kHz}$ , See Figure 35	$R_S = 20\ \Omega$	25°C	32		nV/ $\sqrt{\text{Hz}}$
$B_{OM}$ Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_L = 100\text{ k}\Omega$ , See Figure 34	$C_L = 20\text{ pF}$ , See Figure 34	25°C	34		kHz
			85°C	32		
$B_1$ Unity-gain bandwidth	$V_I = 10\text{ mV}$ , $R_L = 100\text{ k}\Omega$ , See Figure 36	$C_L = 20\text{ pF}$ , See Figure 36	25°C	300		kHz
			85°C	235		
$\phi_m$ Phase margin	$V_I = 10\text{ mV}$ , $C_L = 20\text{ pF}$ , See Figure 36	$f = B_1$ , $R_L = 100\text{ k}\Omega$	-40°C	42°		
			25°C	39°		
			85°C	36°		

**TLV2334I operating characteristics at specified free-air temperature,  $V_{DD} = 5\text{ V}$**

PARAMETER	TEST CONDITIONS	$T_A$	TLV2334I			UNIT	
			MIN	TYP	MAX		
SR Slew rate at unity gain	$V_{IC} = 1\text{ V}$ , $R_L = 100\text{ k}\Omega$ , $C_L = 20\text{ pF}$ , See Figure 34	$V_{I(PP)} = 1\text{ V}$	25°C	0.43		V/ $\mu$ s	
			85°C	0.35			
			25°C	$V_{I(PP)} = 2.5\text{ V}$	0.40		
					85°C		0.32
$V_n$ Equivalent input noise voltage	$f = 1\text{ kHz}$ , See Figure 35	$R_S = 20\ \Omega$	25°C	32		nV/ $\sqrt{\text{Hz}}$	
$B_{OM}$ Maximum output-swing bandwidth	$V_O = V_{OH}$ , $R_L = 100\text{ k}\Omega$ , See Figure 34	$C_L = 20\text{ pF}$ , See Figure 34	25°C	55		kHz	
			85°C	45			
$B_1$ Unity-gain bandwidth	$V_I = 10\text{ mV}$ , $R_L = 100\text{ k}\Omega$ , See Figure 36	$C_L = 20\text{ pF}$ , See Figure 36	25°C	525		kHz	
			85°C	370			
$\phi_m$ Phase margin	$V_I = 10\text{ mV}$ , $C_L = 20\text{ pF}$ , See Figure 36	$f = B_1$ , $R_L = 100\text{ k}\Omega$	-40°C	43°			
			25°C	40°			
			85°C	38°			

**TLV2332, TLV2332Y, TLV2334, TLV2334Y**  
**LinCMOS™ LOW-VOLTAGE MEDIUM-POWER**  
**OPERATIONAL AMPLIFIERS**

SLOS189 – FEBRUARY 1997

**TLV2332Y electrical characteristics,  $T_A = 25^\circ\text{C}$**

PARAMETER	TEST CONDITIONS	TLV2332Y						UNIT
		$V_{DD} = 3\text{ V}$			$V_{DD} = 5\text{ V}$			
		MIN	TYP	MAX	MIN	TYP	MAX	
$V_{IO}$ Input offset voltage	$V_O = 1\text{ V}$ , $R_S = 50\ \Omega$ , $V_{IC} = 1\text{ V}$ , $R_L = 100\text{ k}\Omega$	0.6			1.1			mV
$I_{IO}$ Input offset current (see Note 4)	$V_O = 1\text{ V}$ , $V_{IC} = 1\text{ V}$	0.1			0.1			pA
$I_{IB}$ Input bias current (see Note 4)	$V_O = 1\text{ V}$ , $V_{IC} = 1\text{ V}$	0.6			0.6			pA
$V_{ICR}$ Common-mode input voltage range (see Note 5)		-0.3 to 2.3			-0.3 to 4.2			V
$V_{OH}$ High-level output voltage	$V_{IC} = 1\text{ V}$ , $I_{OH} = -1\text{ mA}$ , $V_{ID} = 100\text{ mV}$	1.9			3.9			V
$V_{OL}$ Low-level output voltage	$V_{IC} = 1\text{ V}$ , $I_{OL} = 1\text{ mA}$ , $V_{ID} = 100\text{ mV}$	115			95			mV
$A_{VD}$ Large-signal differential voltage amplification	$V_{IC} = 1\text{ V}$ , See Note 6, $R_L = 100\text{ k}\Omega$	83			170			V/mV
CMRR Common-mode rejection ratio	$V_O = 1\text{ V}$ , $R_S = 50\ \Omega$ , $V_{IC} = V_{ICRmin}$	92			91			dB
$k_{SVR}$ Supply-voltage rejection ratio ( $\Delta V_{DD}/\Delta V_{ID}$ )	$V_O = 1\text{ V}$ , $R_S = 50\ \Omega$ , $V_{IC} = 1\text{ V}$	94			94			dB
$I_{DD}$ Supply current	$V_O = 1\text{ V}$ , No load, $V_{IC} = 1\text{ V}$	160			210			$\mu\text{A}$

- NOTES: 4. The typical values of input bias current and input offset current below 5 pA are determined mathematically.  
5. This range also applies to each input individually.  
6. At  $V_{DD} = 5\text{ V}$ ,  $V_O = 0.25\text{ V}$  to  $2\text{ V}$ ; at  $V_{DD} = 3\text{ V}$ ,  $V_O = 0.5\text{ V}$  to  $1.5\text{ V}$ .



TLV2334Y electrical characteristics,  $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	TLV2334Y						UNIT
		$V_{DD} = 3\text{ V}$			$V_{DD} = 5\text{ V}$			
		MIN	TYP	MAX	MIN	TYP	MAX	
$V_{IO}$ Input offset voltage	$V_O = 1\text{ V}$ , $R_S = 50\ \Omega$ , $V_{IC} = 1\text{ V}$ , $R_L = 100\text{ k}\Omega$		0.6			1.1		mV
$I_{IO}$ Input offset current (see Note 4)	$V_O = 1\text{ V}$ , $V_{IC} = 1\text{ V}$		0.1			0.1		pA
$I_{IB}$ Input bias current (see Note 4)	$V_O = 1\text{ V}$ , $V_{IC} = 1\text{ V}$		0.6			0.6		pA
$V_{ICR}$ Common-mode input voltage range (see Note 5)			-0.3 to 2.3			-0.3 to 4.2		V
$V_{OH}$ High-level output voltage	$V_{IC} = 1\text{ V}$ , $I_{OH} = -1\text{ mA}$ , $V_{ID} = 100\text{ mV}$		1.9			3.9		V
$V_{OL}$ Low-level output voltage	$V_{IC} = 1\text{ V}$ , $I_{OL} = 1\text{ mA}$ , $V_{ID} = -100\text{ mV}$		115			95		mV
$A_{VD}$ Large-signal differential voltage amplification	$V_{IC} = 1\text{ V}$ , See Note 6, $R_L = 100\text{ k}\Omega$		83			170		V/mV
CMRR Common-mode rejection ratio	$V_O = 1\text{ V}$ , $R_S = 50\ \Omega$ , $V_{IC} = V_{ICRmin}$		92			91		dB
$k_{SVR}$ Supply-voltage rejection ratio ( $\Delta V_{DD}/\Delta V_{ID}$ )	$V_{IC} = 1\text{ V}$ , $R_S = 50\ \Omega$ , $V_O = 1\text{ V}$		94			94		dB
$I_{DD}$ Supply current	$V_O = 1\text{ V}$ , No load, $V_{IC} = 1\text{ V}$		320			420		$\mu\text{A}$

- NOTES: 4. The typical values of input bias current offset current below 5 pA are determined mathematically.  
 5. This range also applies to each input individually.  
 6. At  $V_{DD} = 5\text{ V}$ ,  $V_O = 0.25\text{ V}$  to  $2\text{ V}$ ; at  $V_{DD} = 3\text{ V}$ ,  $V_O = 0.5\text{ V}$  to  $1.5\text{ V}$ .

**TYPICAL CHARACTERISTICS**

**Table of Graphs**

		<b>FIGURE</b>	
$V_{IO}$	Input offset voltage	Distribution	1 – 4
$\alpha_{VIO}$	Input offset voltage temperature coefficient	Distribution	5 – 8
$I_{IB}$	Input bias current	vs Free-air temperature	9
$I_{IO}$	Input offset current	vs Free-air temperature	9
$V_{IC}$	Common-mode input voltage	vs Supply voltage	10
$V_{OH}$	High-level output voltage	vs High-level output current	11
		vs Supply voltage	12
		vs Free-air temperature	13
$V_{OL}$	Low-level output voltage	vs Common-mode input voltage	14
		vs Free-air temperature	15, 16
		vs Differential input voltage	17
		vs Low-level output current	18
$A_{VD}$	Large-signal differential voltage amplification	vs Supply voltage	19
		vs Free-air temperature	20
		vs Frequency	21, 22
$I_{DD}$	Supply current	vs Supply voltage	23
		vs Free-air temperature	24
SR	Slew rate	vs Supply voltage	25
		vs Free-air temperature	26
$V_{O(PP)}$	Maximum peak-to-peak output voltage	vs Frequency	27
$B_1$	Unity-gain bandwidth	vs Supply voltage	28
		vs Free-air temperature	29
$\phi_m$	Phase margin	vs Supply voltage	30
		vs Free-air temperature	31
		vs Load capacitance	32
	Phase shift	vs Frequency	21, 22
$V_n$	Equivalent input noise voltage	vs Frequency	33

TYPICAL CHARACTERISTICS

DISTRIBUTION OF TLV2332  
 INPUT OFFSET VOLTAGE

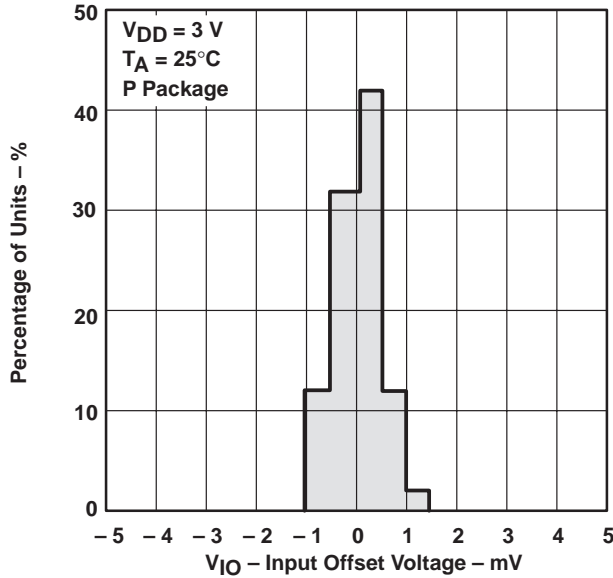


Figure 1

DISTRIBUTION OF TLV2332  
 INPUT OFFSET VOLTAGE

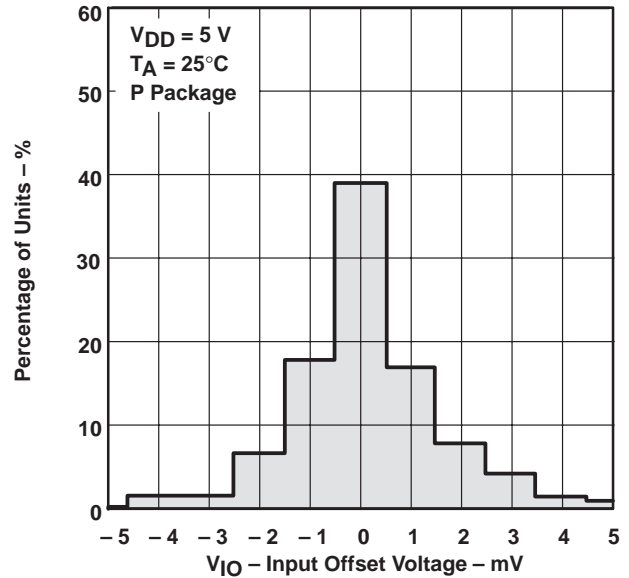


Figure 2

DISTRIBUTION OF TLV2334  
 INPUT OFFSET VOLTAGE

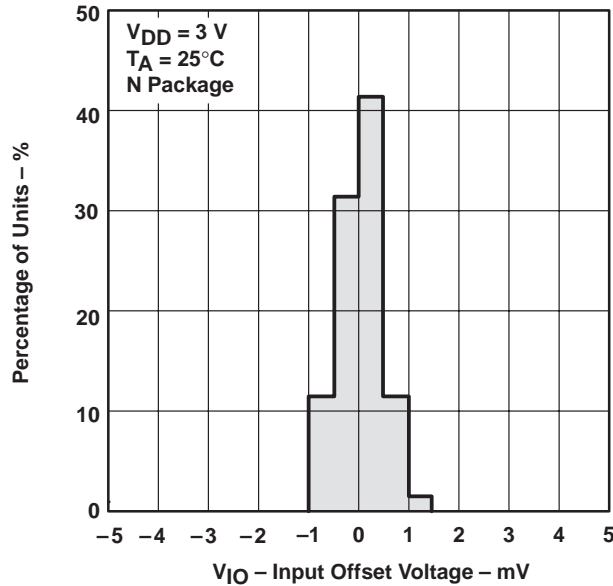


Figure 3

DISTRIBUTION OF TLV2334  
 INPUT OFFSET VOLTAGE

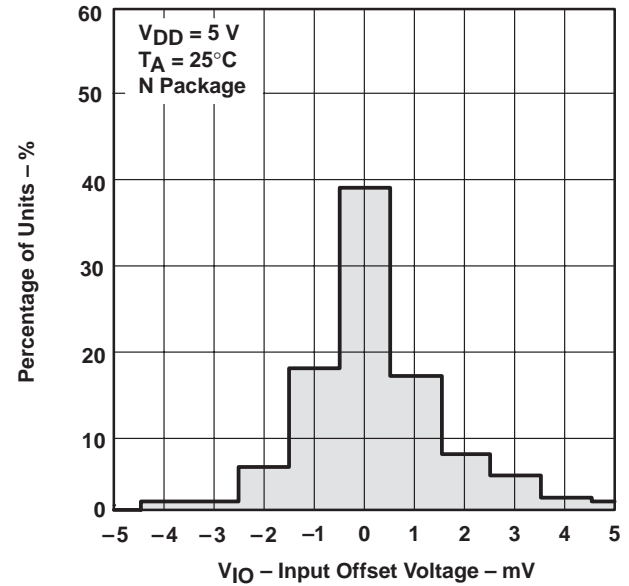


Figure 4

TYPICAL CHARACTERISTICS

DISTRIBUTION OF TLV2332  
 INPUT OFFSET VOLTAGE  
 TEMPERATURE COEFFICIENT

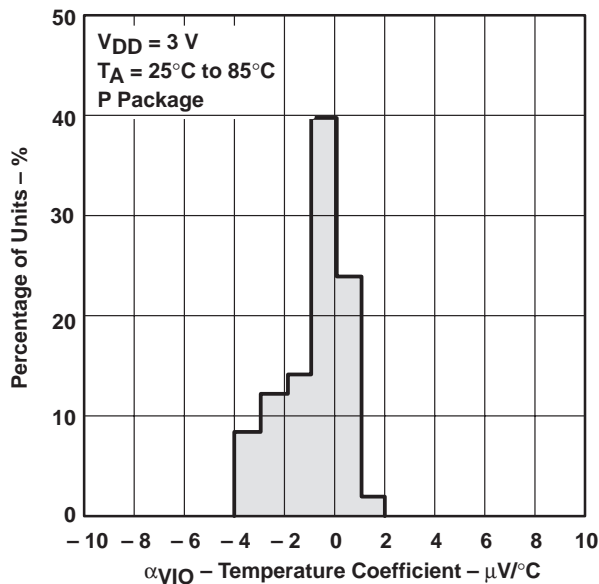


Figure 5

DISTRIBUTION OF TLV2332  
 INPUT OFFSET VOLTAGE  
 TEMPERATURE COEFFICIENT

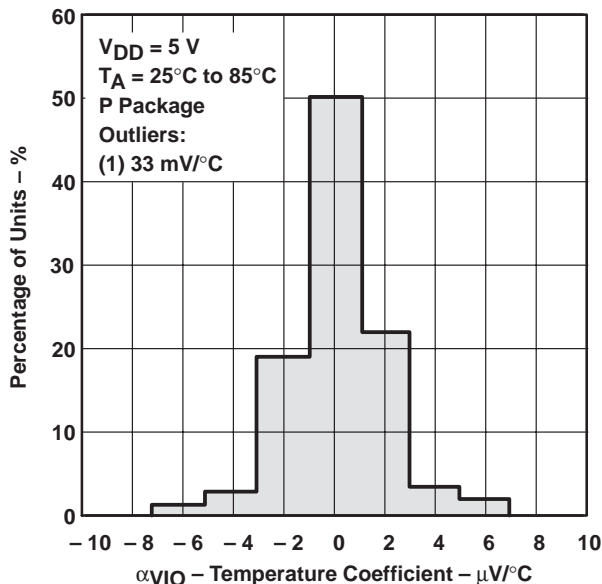


Figure 6

DISTRIBUTION OF TLV2334  
 INPUT OFFSET VOLTAGE  
 TEMPERATURE COEFFICIENT

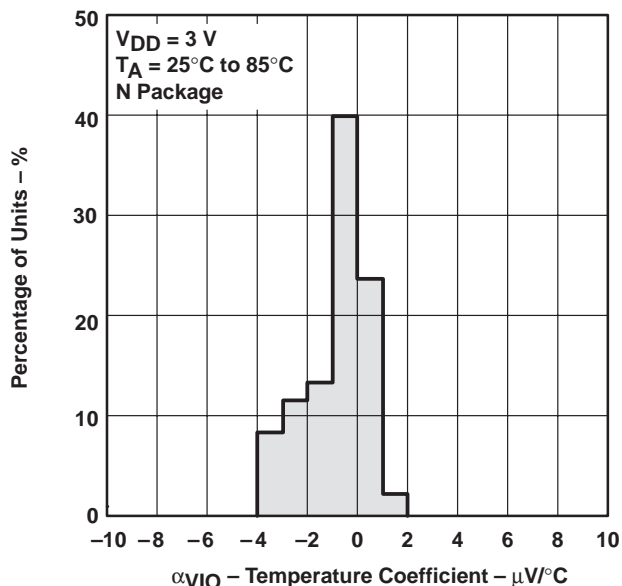


Figure 7

DISTRIBUTION OF TLV2334  
 INPUT OFFSET VOLTAGE  
 TEMPERATURE COEFFICIENT

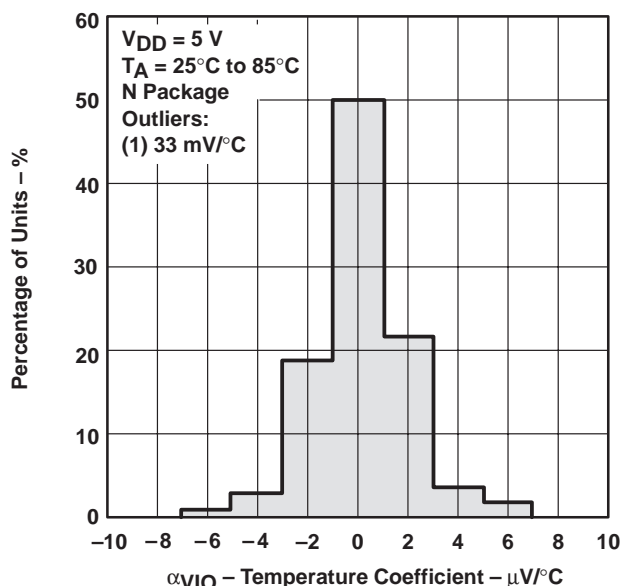
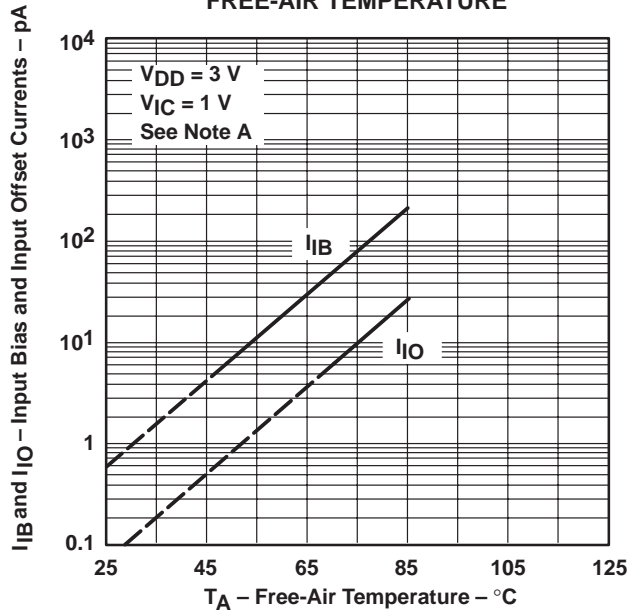


Figure 8

TYPICAL CHARACTERISTICS

INPUT BIAS CURRENT AND INPUT OFFSET CURRENT  
 VS  
 FREE-AIR TEMPERATURE



NOTE: The typical values of input bias current and input offset current below 5 pA were determined mathematically.

Figure 9

COMMON-MODE INPUT VOLTAGE  
 VS  
 SUPPLY VOLTAGE

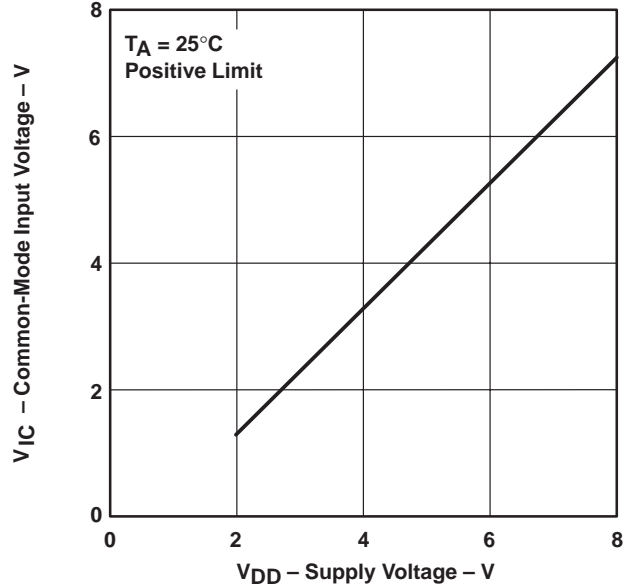


Figure 10

HIGH-LEVEL OUTPUT VOLTAGE  
 VS  
 HIGH-LEVEL OUTPUT CURRENT

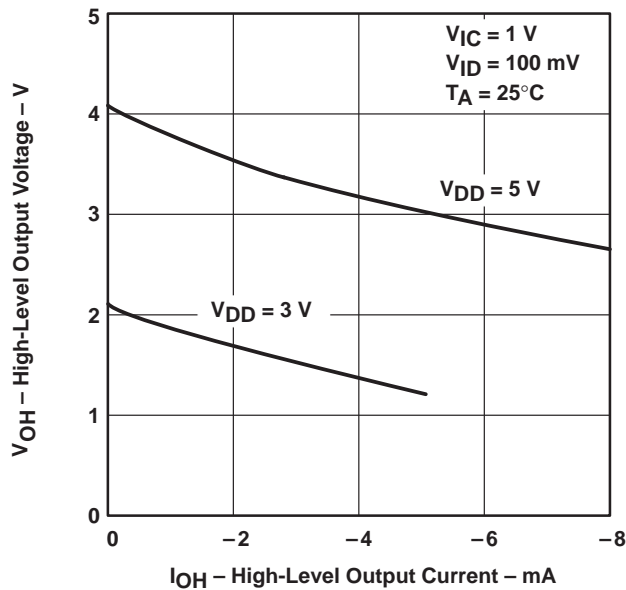


Figure 11

HIGH-LEVEL OUTPUT VOLTAGE  
 VS  
 SUPPLY VOLTAGE

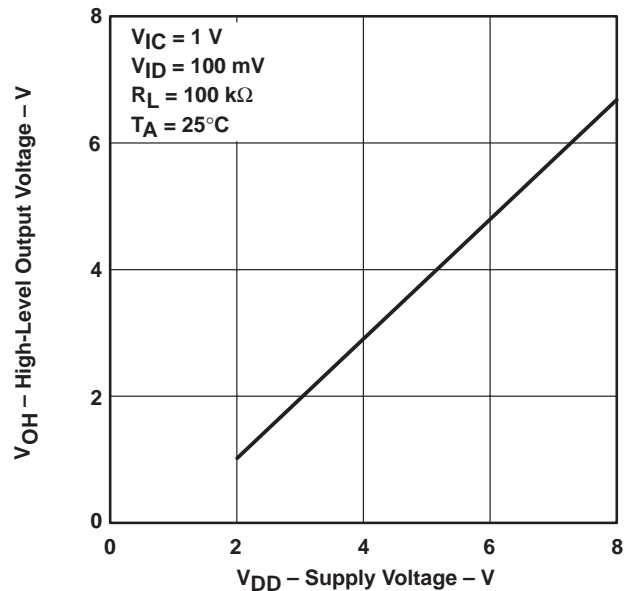


Figure 12

TYPICAL CHARACTERISTICS

HIGH-LEVEL OUTPUT VOLTAGE  
 vs  
 FREE-AIR TEMPERATURE

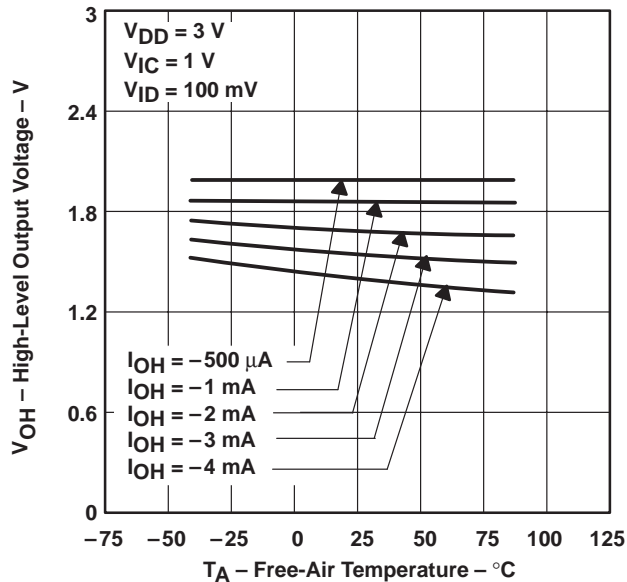


Figure 13

LOW-LEVEL OUTPUT VOLTAGE  
 vs  
 COMMON-MODE INPUT VOLTAGE

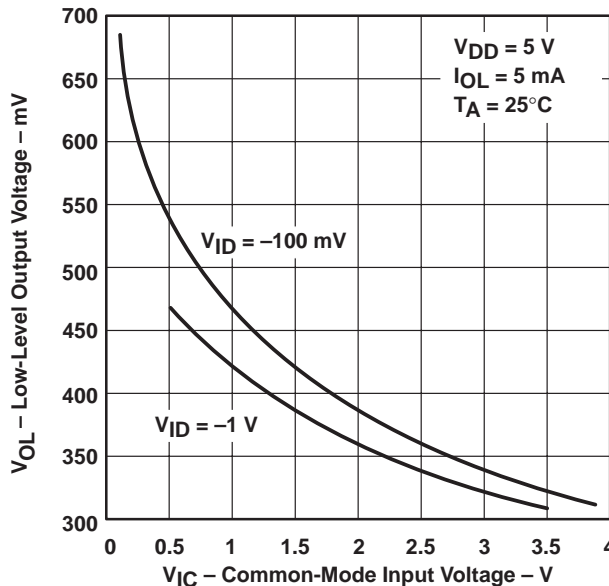


Figure 14

LOW-LEVEL OUTPUT VOLTAGE  
 vs  
 FREE-AIR TEMPERATURE

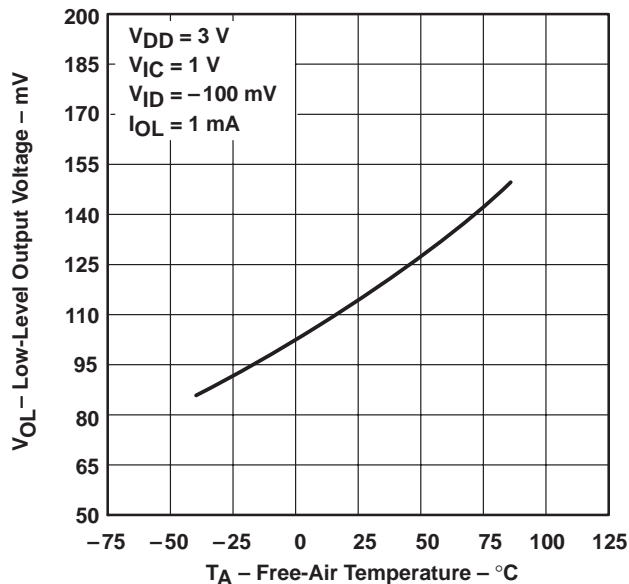


Figure 15

LOW-LEVEL OUTPUT VOLTAGE  
 vs  
 FREE-AIR TEMPERATURE

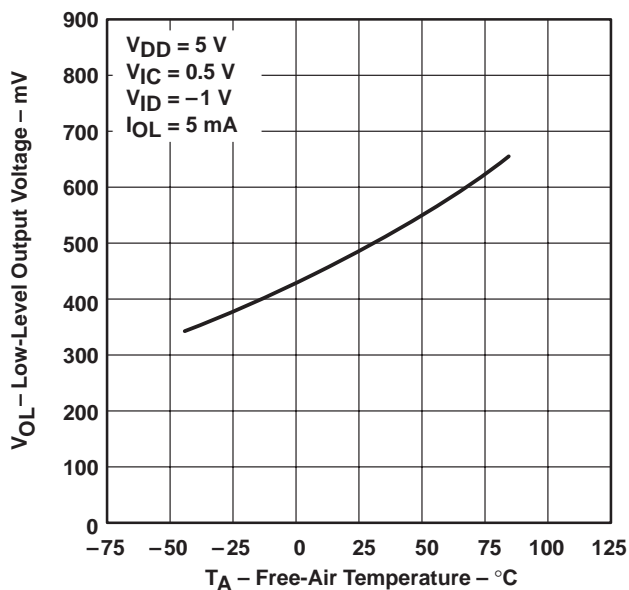


Figure 16



TYPICAL CHARACTERISTICS

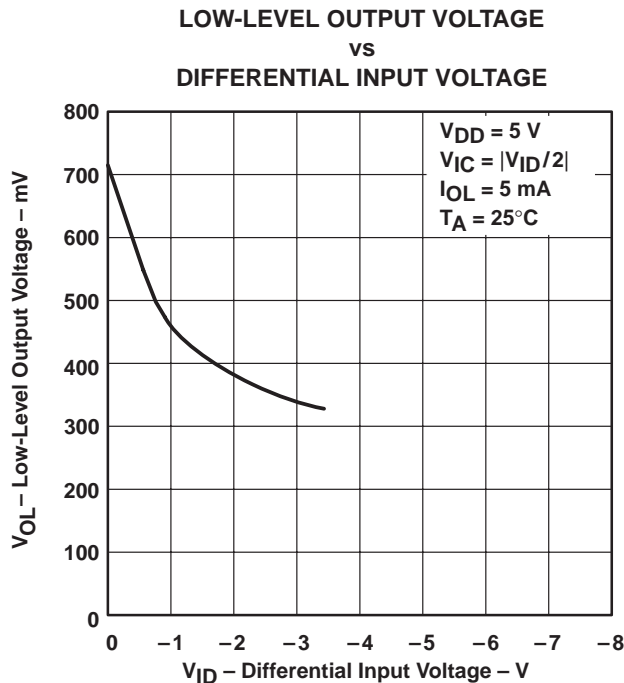


Figure 17

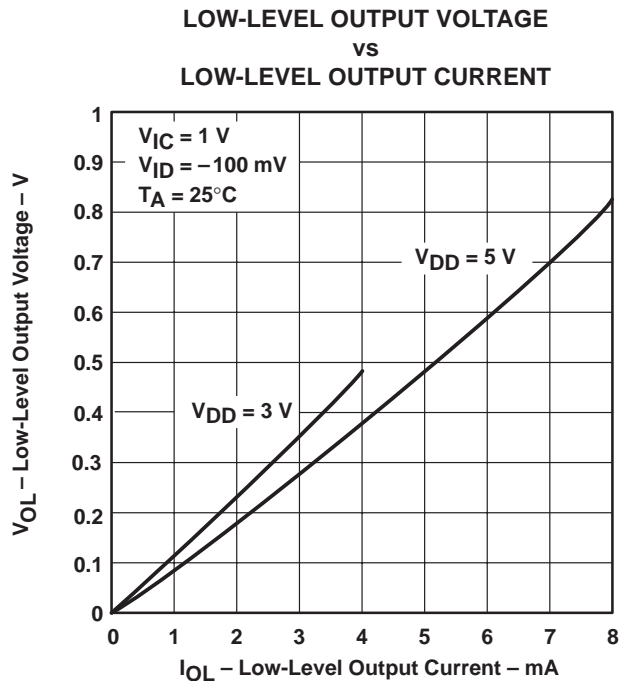


Figure 18

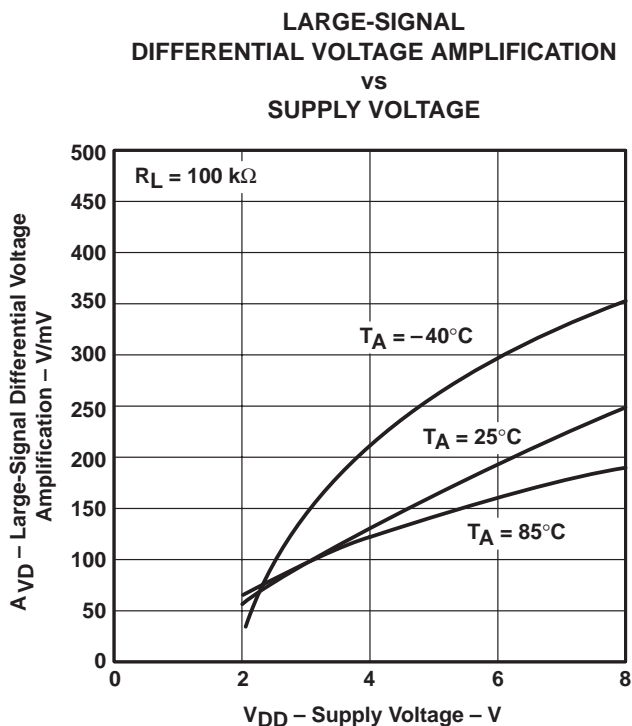


Figure 19

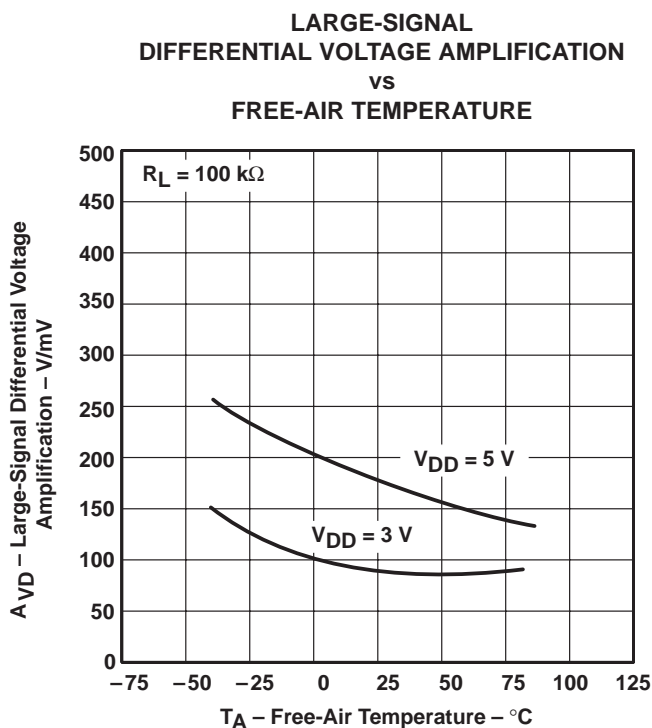


Figure 20

**TYPICAL CHARACTERISTICS**

**LARGE-SIGNAL DIFFERENTIAL VOLTAGE  
 AMPLIFICATION AND PHASE SHIFT**

vs  
**FREQUENCY**

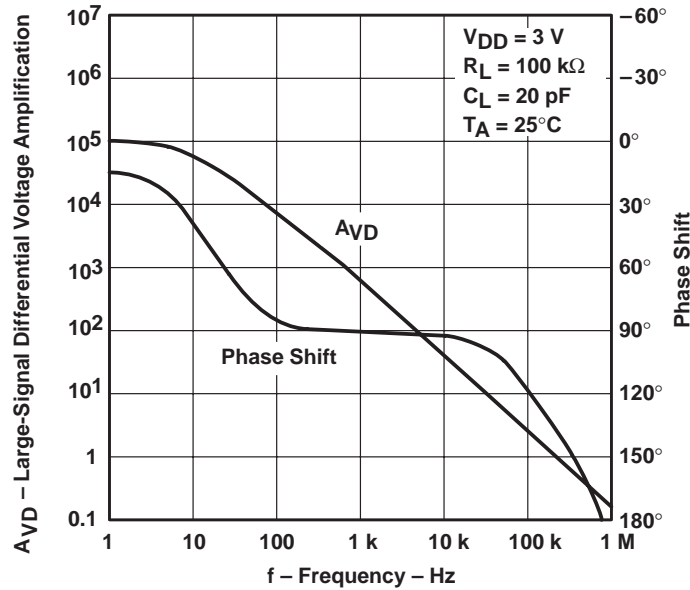


Figure 21

**LARGE-SIGNAL DIFFERENTIAL VOLTAGE  
 AMPLIFICATION AND PHASE SHIFT**

vs  
**FREQUENCY**

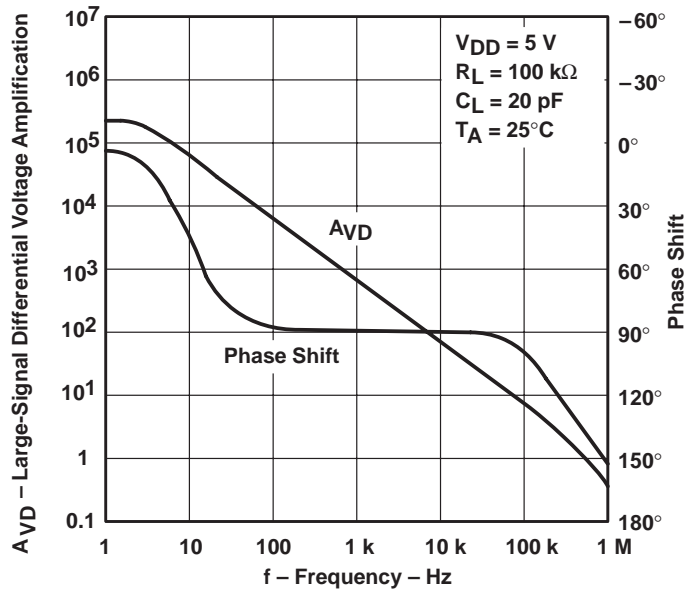


Figure 22

TYPICAL CHARACTERISTICS

SUPPLY CURRENT  
 vs  
 SUPPLY VOLTAGE

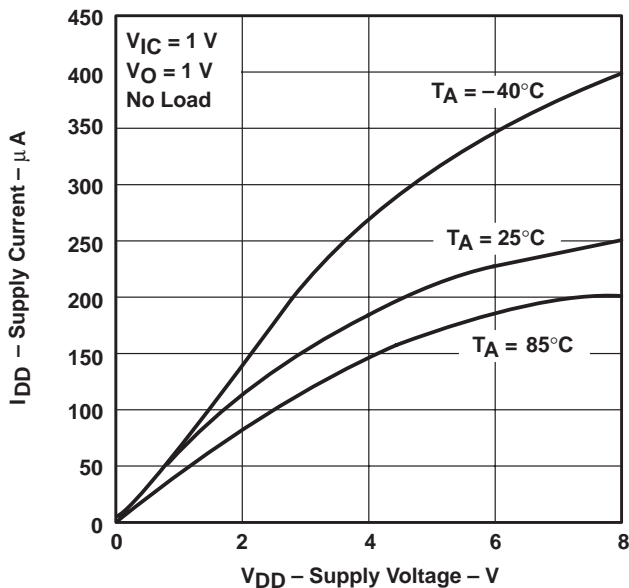


Figure 23

SUPPLY CURRENT  
 vs  
 FREE-AIR TEMPERATURE

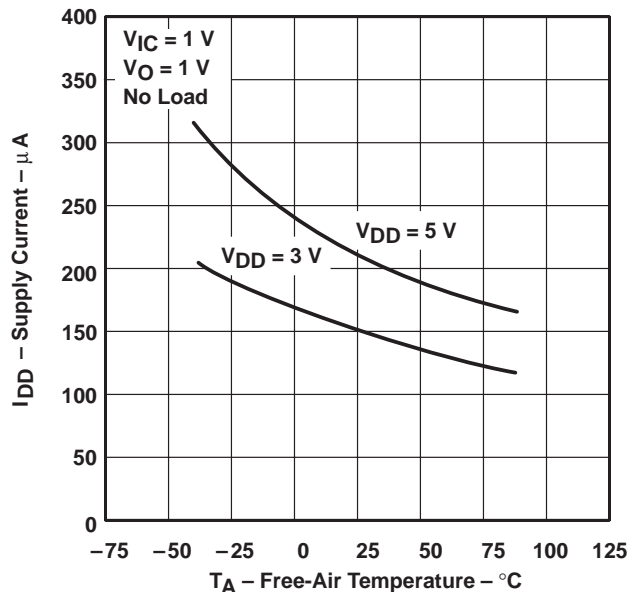


Figure 24

SLEW RATE  
 vs  
 SUPPLY VOLTAGE

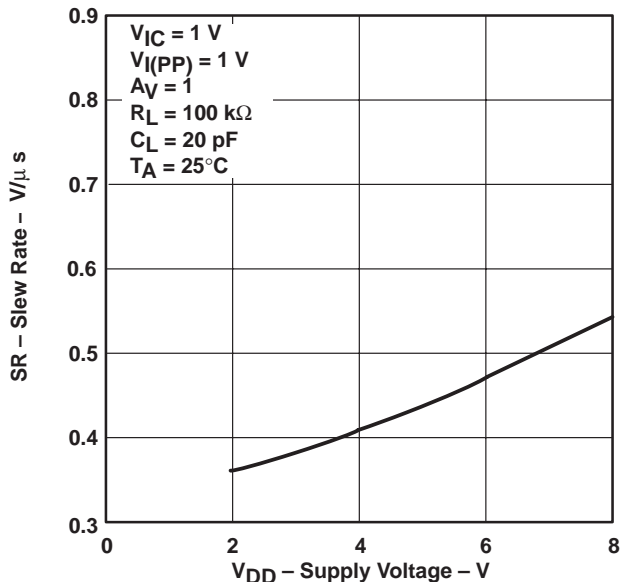


Figure 25

SLEW RATE  
 vs  
 FREE-AIR TEMPERATURE

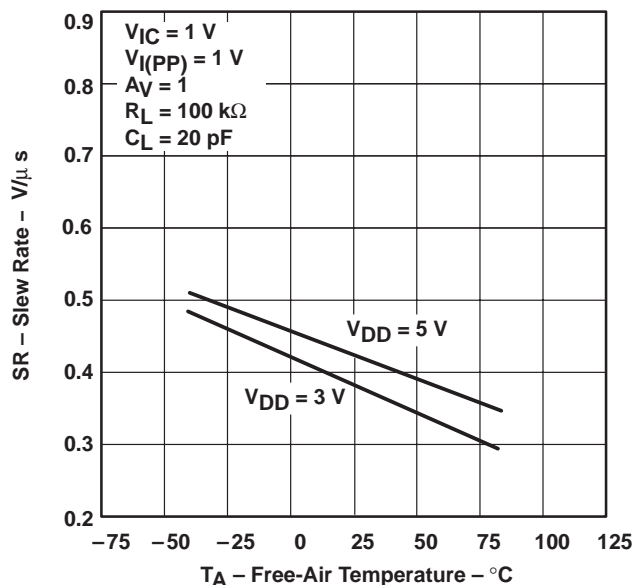


Figure 26

TYPICAL CHARACTERISTICS

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE  
 vs  
 FREQUENCY

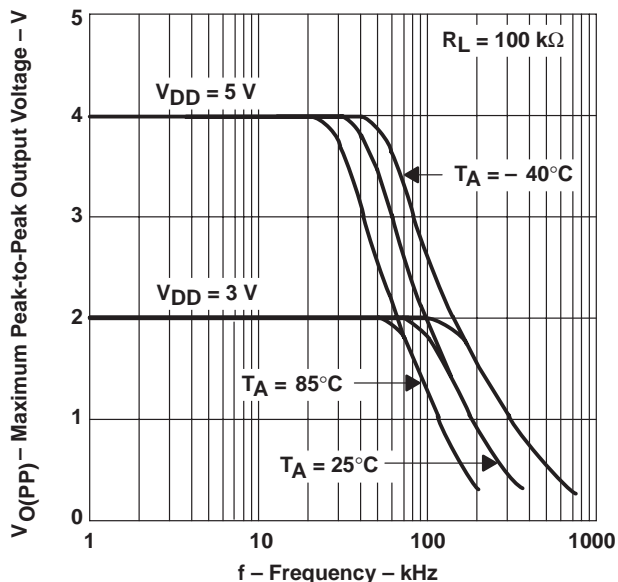


Figure 27

UNITY-GAIN BANDWIDTH  
 vs  
 SUPPLY VOLTAGE

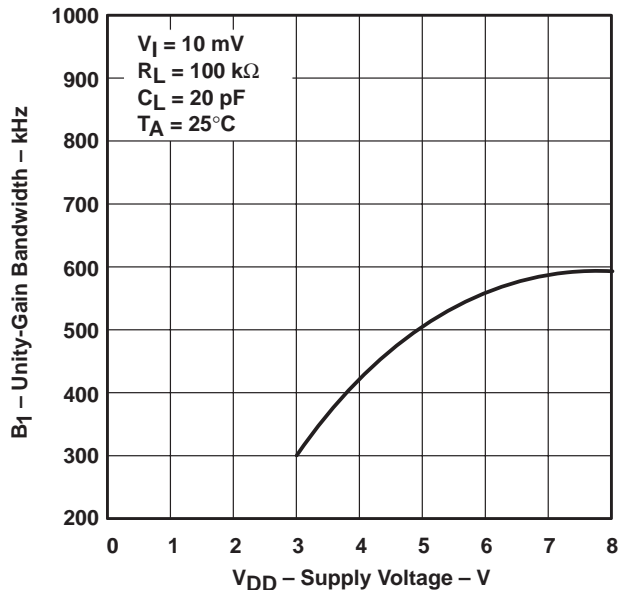


Figure 28

UNITY-GAIN BANDWIDTH  
 vs  
 FREE-AIR TEMPERATURE

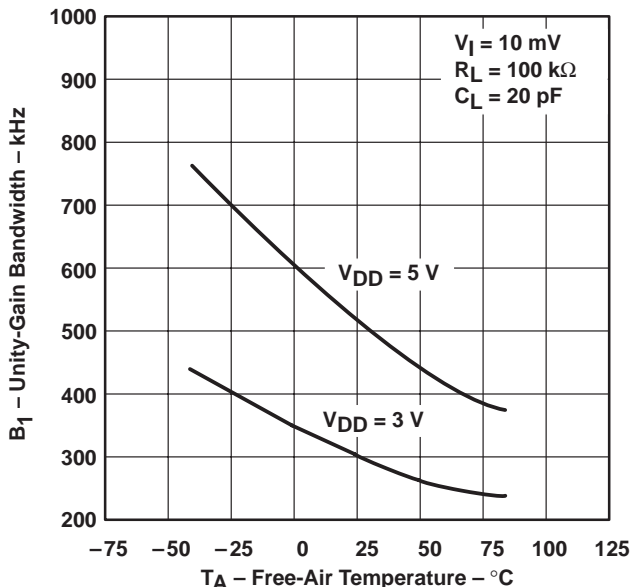


Figure 29

TYPICAL CHARACTERISTICS

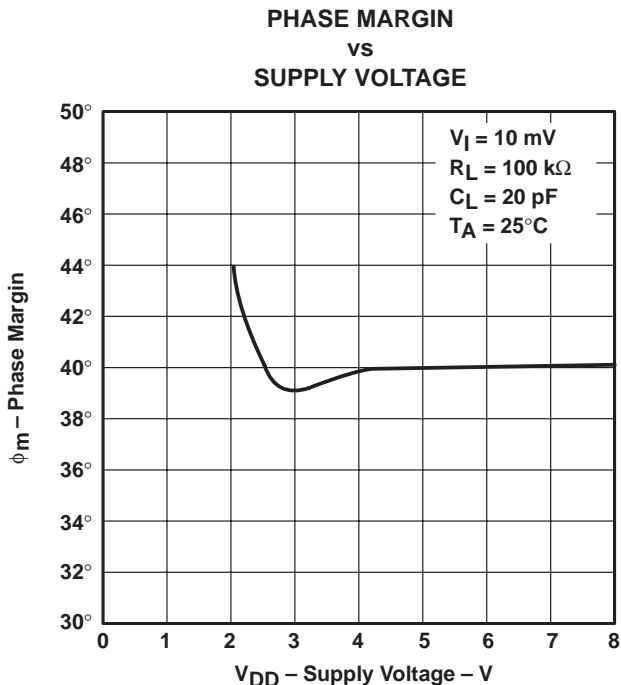


Figure 30

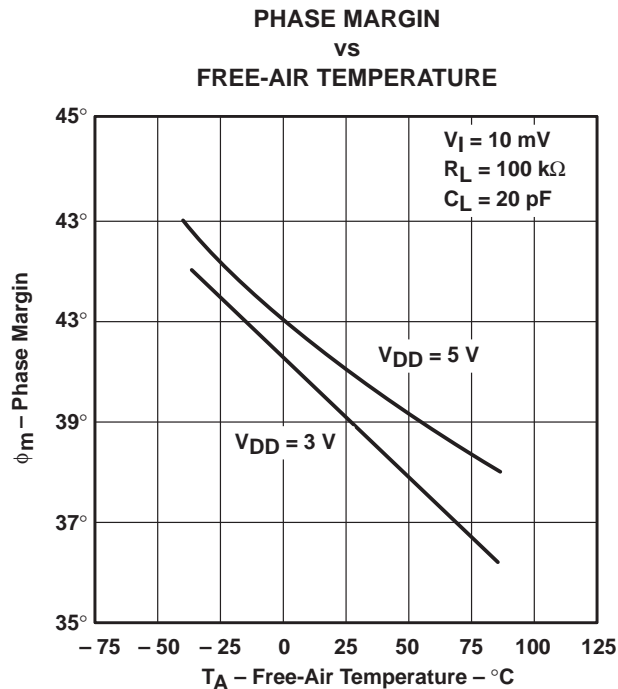


Figure 31

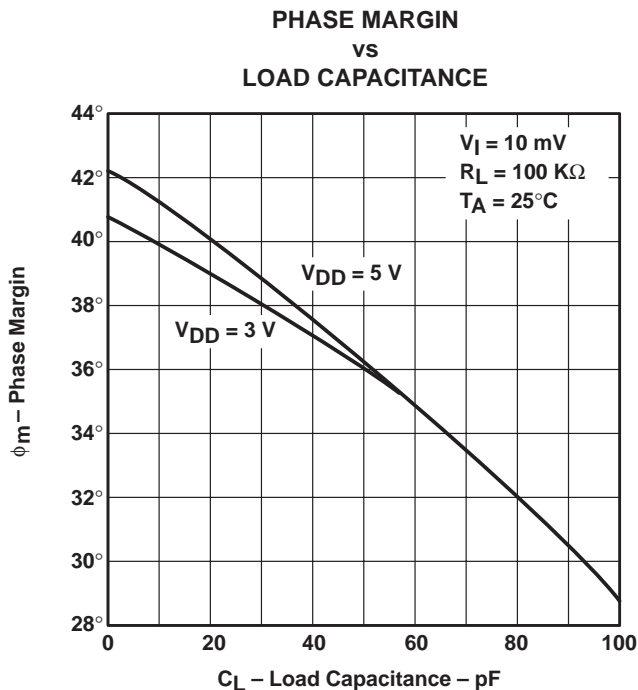


Figure 32

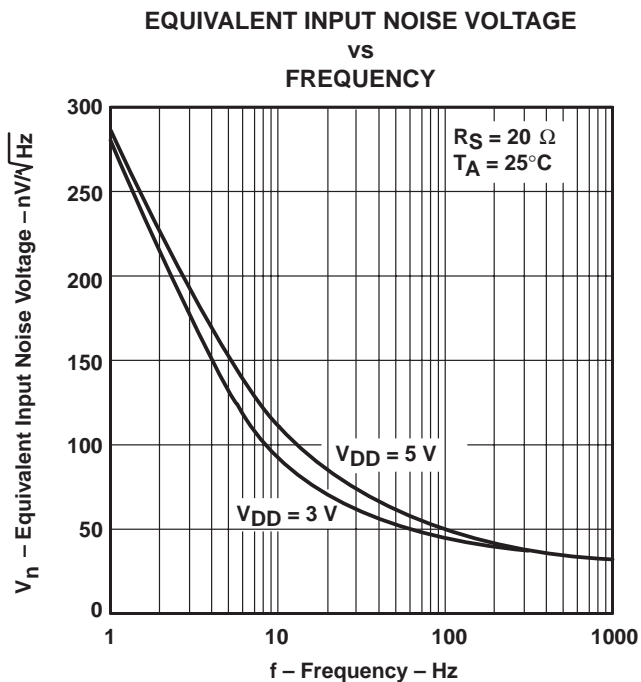


Figure 33

PARAMETER MEASUREMENT INFORMATION

single-supply versus split-supply test circuits

Because the TLV233x is optimized for single-supply operation, circuit configurations used for the various tests often present some inconvenience since the input signal, in many cases, must be offset from ground. This inconvenience can be avoided by testing the device with split supplies and the output load tied to the negative rail. A comparison of single-supply versus split-supply test circuits is shown below. The use of either circuit gives the same result.

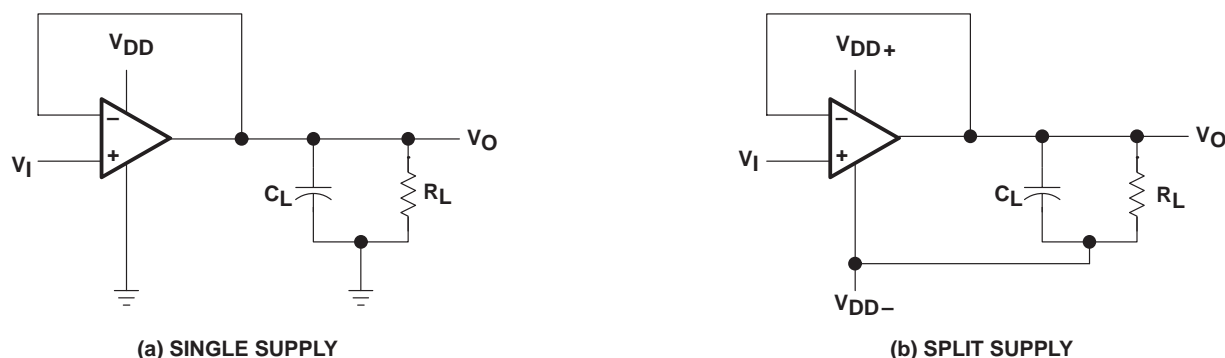


Figure 34. Unity-Gain Amplifier

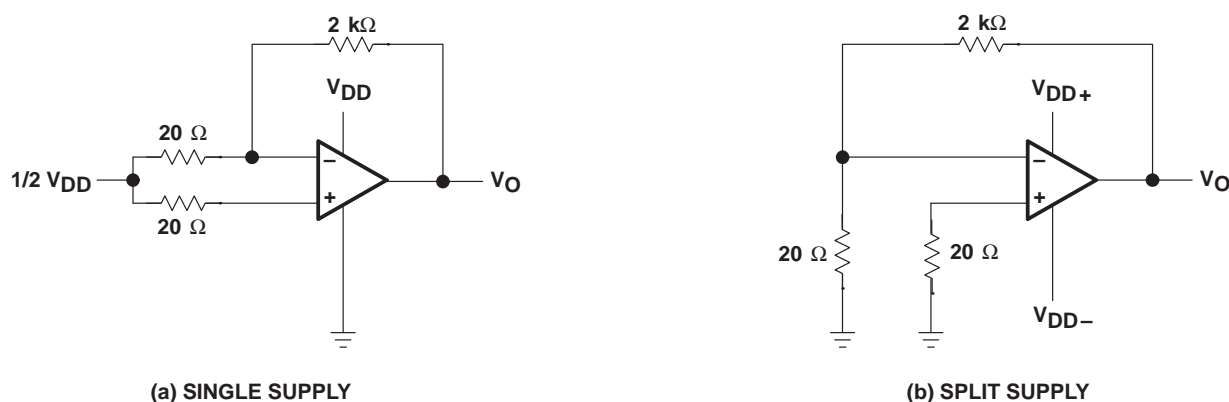


Figure 35. Noise-Test Circuit

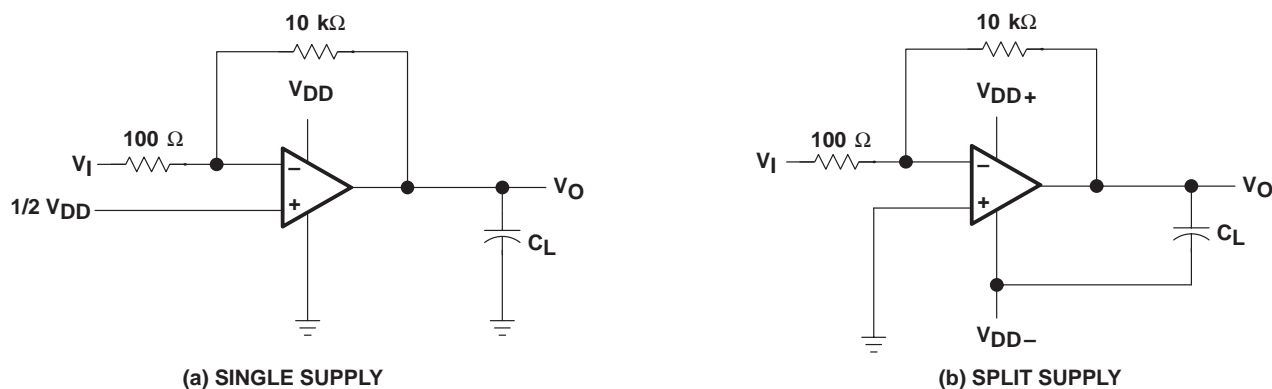


Figure 36. Gain-of-100 Inverting Amplifier

## PARAMETER MEASUREMENT INFORMATION

### input bias current

Because of the high input impedance of the TLV233x operational amplifier, attempts to measure the input bias current can result in erroneous readings. The bias current at normal ambient temperature is typically less than 1 pA, a value that is easily exceeded by leakages on the test socket. Two suggestions are offered to avoid erroneous measurements:

- Isolate the device from other potential leakage sources. Use a grounded shield around and between the device inputs (see Figure 37). Leakages that would otherwise flow to the inputs are shunted away.
- Compensate for the leakage of the test socket by actually performing an input bias current test (using a picoammeter) with no device in the test socket. The actual input bias current can then be calculated by subtracting the open-socket leakage readings from the readings obtained with a device in the test socket.

Many automatic testers as well as some bench-top operational amplifier testers use the servo-loop technique with a resistor in series with the device input to measure the input bias current (the voltage drop across the series resistor is measured and the bias current is calculated). This method requires that a device be inserted into a test socket to obtain a correct reading; therefore, an open-socket reading is not feasible using this method.

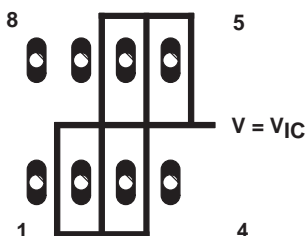


Figure 37. Isolation Metal Around Device Inputs (P package)

### low-level output voltage

To obtain low-level supply-voltage operation, some compromise is necessary in the input stage. This compromise results in the device low-level output voltage being dependent on both the common-mode input voltage level as well as the differential input voltage level. When attempting to correlate low-level output readings with those quoted in the electrical specifications, these two conditions should be observed. If conditions other than these are to be used, please refer to the Typical Characteristics section of this data sheet.

### input offset voltage temperature coefficient

Erroneous readings often result from attempts to measure temperature coefficient of input offset voltage. This parameter is actually a calculation using input offset voltage measurements obtained at two different temperatures. When one (or both) of the temperatures is below freezing, moisture can collect on both the device and the test socket. This moisture results in leakage and contact resistance which can cause erroneous input offset voltage readings. The isolation techniques previously mentioned have no effect on the leakage since the moisture also covers the isolation metal itself, thereby rendering it useless. These measurements should be performed at temperatures above freezing to minimize error.

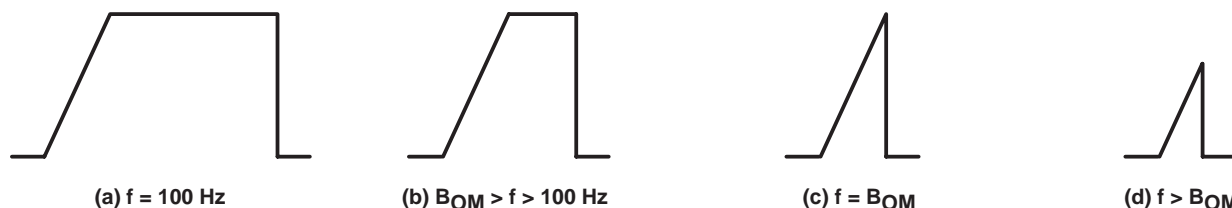
### full-power response

Full-power response, the frequency above which the operational amplifier slew rate limits the output voltage swing, is often specified two ways: full-linear response and full-peak response. The full-linear response is

**PARAMETER MEASUREMENT INFORMATION**

generally measured by monitoring the distortion level of the output while increasing the frequency of a sinusoidal input signal until the maximum frequency is found above which the output contains significant distortion. The full-peak response is defined as the maximum output frequency, without regard to distortion, above which full peak-to-peak output swing cannot be maintained.

Because there is no industry-wide accepted value for significant distortion, the full-peak response is specified in this data sheet and is measured using the circuit of Figure 34. The initial setup involves the use of a sinusoidal input to determine the maximum peak-to-peak output of the device (the amplitude of the sinusoidal wave is increased until clipping occurs). The sinusoidal wave is then replaced with a square wave of the same amplitude. The frequency is then increased until the maximum peak-to-peak output can no longer be maintained (Figure 38). A square wave is used to allow a more accurate determination of the point at which the maximum peak-to-peak output is reached.



**Figure 38. Full-Power-Response Output Signal**

**test time**

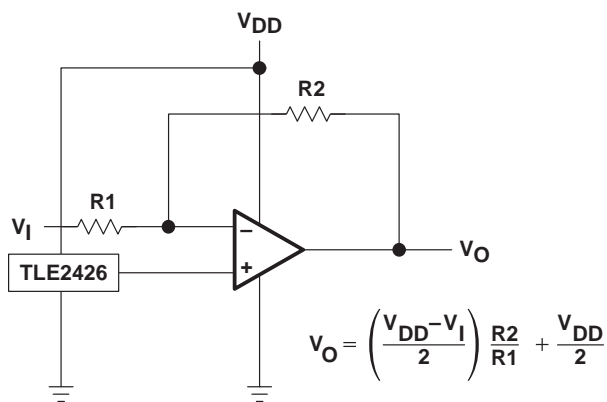
Inadequate test time is a frequent problem, especially when testing CMOS devices in a high-volume, short-test-time environment. Internal capacitances are inherently higher in CMOS than in bipolar and BiFET devices and require longer test times than their bipolar and BiFET counterparts. The problem becomes more pronounced with reduced supply levels and lower temperatures.

**APPLICATION INFORMATION**

**single-supply operation**

While the TLV233x performs well using dual-power supplies (also called balanced or split supplies), the design is optimized for single-supply operation. This includes an input common-mode voltage range that encompasses ground as well as an output voltage range that pulls down to ground. The supply voltage range extends down to 2 V, thus allowing operation with supply levels commonly available for TTL and HCMOS.

Many single-supply applications require that a voltage be applied to one input to establish a reference level that is above ground. This virtual ground can be generated using two large resistors, but a preferred technique is to use a virtual-ground generator such as the TLE2426 (see Figure 39).



**Figure 39. Inverting Amplifier With Voltage Reference**

$$V_O = \left( \frac{V_{DD} - V_I}{2} \right) \frac{R_2}{R_1} + \frac{V_{DD}}{2}$$

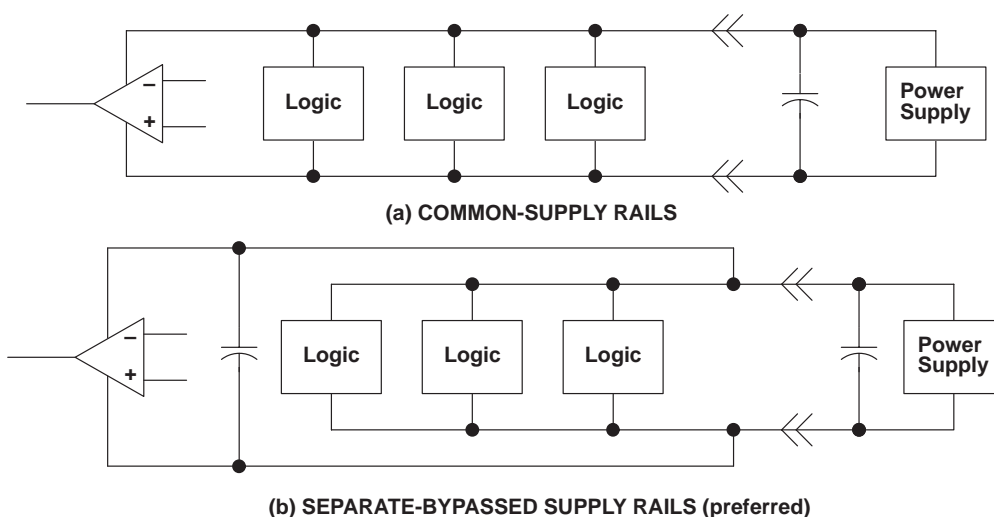


## APPLICATION INFORMATION

### single-supply operation (continued)

The TLV2426 supplies an accurate voltage equal to  $V_{DD}/2$ , while consuming very little power and is suitable for supply voltages of greater than 4 V. The TLV233x works well in conjunction with digital logic; however, when powering both linear devices and digital logic from the same power supply, the following precautions are recommended:

- Power the linear devices from separate bypassed supply lines (see Figure 40); otherwise, the linear device supply rails can fluctuate due to voltage drops caused by high switching currents in the digital logic.
- Use proper bypass techniques to reduce the probability of noise-induced errors. Single capacitive decoupling is often adequate; however, RC decoupling may be necessary in high-frequency applications.



**Figure 40. Common Versus Separate Supply Rails**

### input characteristics

The TLV233x is specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction. Exceeding this specified range is a common problem, especially in single-supply operation. The lower range limit includes the negative rail, while the upper range limit is specified at  $V_{DD} - 1$  V at  $T_A = 25^\circ\text{C}$  and at  $V_{DD} - 1.2$  V at all other temperatures.

The use of the polysilicon-gate process and the careful input circuit design gives the TLV233x very good input offset voltage drift characteristics relative to conventional metal-gate processes. Offset voltage drift in CMOS devices is highly influenced by threshold voltage shifts caused by polarization of the phosphorus dopant implanted in the oxide. Placing the phosphorus dopant in a conductor (such as a polysilicon gate) alleviates the polarization problem, thus reducing threshold voltage shifts by more than an order of magnitude. The offset voltage drift with time has been calculated to be typically  $0.1 \mu\text{V}/\text{month}$ , including the first month of operation.

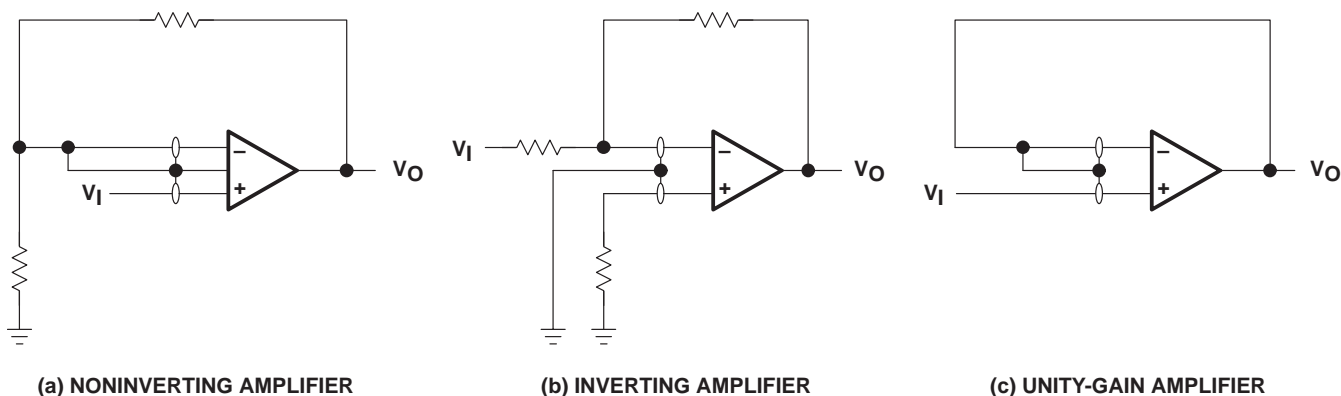
Because of the extremely high input impedance and resulting low bias-current requirements, the TLV233x is well suited for low-level signal processing; however, leakage currents on printed-circuit boards and sockets can easily exceed bias-current requirements and cause a degradation in device performance.

**APPLICATION INFORMATION**

**input characteristics (continued)**

It is good practice to include guard rings around inputs (similar to those of Figure 37 in the Parameter Measurement Information section). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input (see Figure 41).

The inputs of any unused amplifiers should be tied to ground to avoid possible oscillation.



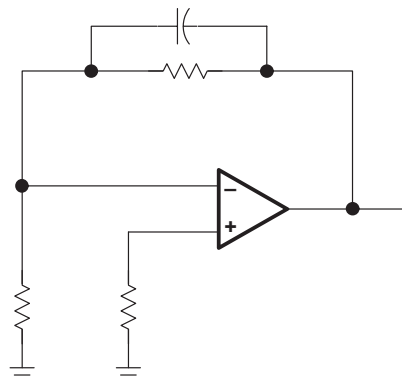
**Figure 41. Guard-Ring Schemes**

**noise performance**

The noise specifications in operational amplifiers circuits are greatly dependent on the current in the first-stage differential amplifier. The low input bias-current requirements of the TLV233x results in a very low noise current, which is insignificant in most applications. This feature makes the device especially favorable over bipolar devices when using values of circuit impedance greater than 50 kΩ, since bipolar devices exhibit greater noise currents.

**feedback**

Operational amplifiers circuits nearly always employ feedback, and since feedback is the first prerequisite for oscillation, caution is appropriate. Most oscillation problems result from driving capacitive loads and ignoring stray input capacitance. A small-value capacitor connected in parallel with the feedback resistor is an effective remedy (see Figure 42). The value of this capacitor is optimized empirically.



**Figure 42. Compensation for Input Capacitance**

**electrostatic-discharge protection**

The TLV233x incorporates an internal electrostatic-discharge (ESD)-protection circuit that prevents functional failures at voltages up to 2000 V as tested under MIL-PRF-38535, Method 3015.2. Care should be exercised, however, when handling these devices as exposure to ESD may result in the degradation of the device parametric performance. The protection circuit also causes the input bias currents to be temperature dependent and have the characteristics of a reverse-biased diode.

## APPLICATION INFORMATION

### latch-up

Because CMOS devices are susceptible to latch-up due to their inherent parasitic thyristors, the TLV233x inputs and outputs are designed to withstand –100-mA surge currents without sustaining latch-up; however, techniques should be used to reduce the chance of latch-up whenever possible. Internal-protection diodes should not by design be forward biased. Applied input and output voltage should not exceed the supply voltage by more than 300 mV. Care should be exercised when using capacitive coupling on pulse generators. Supply transients should be shunted by the use of decoupling capacitors (0.1  $\mu$ F typical) located across the supply rails as close to the device as possible.

The current path established if latch-up occurs is usually between the positive supply rail and ground and can be triggered by surges on the supply lines and/or voltages on either the output or inputs that exceed the supply voltage. Once latch-up occurs, the current flow is limited only by the impedance of the power supply and the forward resistance of the parasitic thyristor and usually results in the destruction of the device. The chance of latch-up occurring increases with increasing temperature and supply voltages.

### output characteristics

The output stage of the TLV233x is designed to sink and source relatively high amounts of current (see Typical Characteristics). If the output is subjected to a short-circuit condition, this high-current capability can cause device damage under certain conditions. Output current capability increases with supply voltage.

Although the TLV233x possesses excellent high-level output voltage and current capability, methods are available for boosting this capability if needed. The simplest method involves the use of a pullup resistor ( $R_P$ ) connected from the output to the positive supply rail (see Figure 43). There are two disadvantages to the use of this circuit. First, the NMOS pulldown transistor N4 (see equivalent schematic) must sink a comparatively large amount of current. In this circuit, N4 behaves like a linear resistor with an on resistance between approximately 60  $\Omega$  and 180  $\Omega$ , depending on how hard the operational amplifier input is driven. With very low values of  $R_P$ , a voltage offset from 0 V at the output occurs. Secondly, pullup resistor  $R_P$  acts as a drain load to N4 and the gain of the operational amplifier is reduced at output voltage levels where N5 is not supplying the output current.

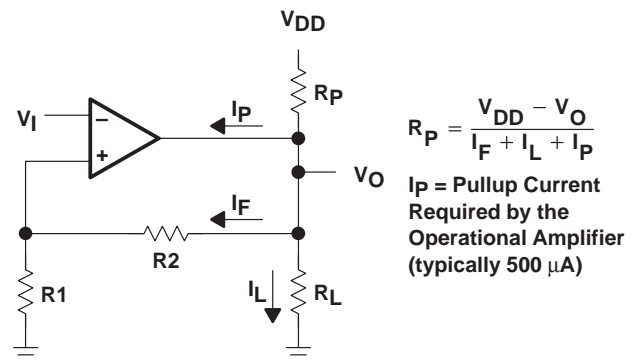


Figure 43. Resistive Pullup to Increase  $V_{OH}$

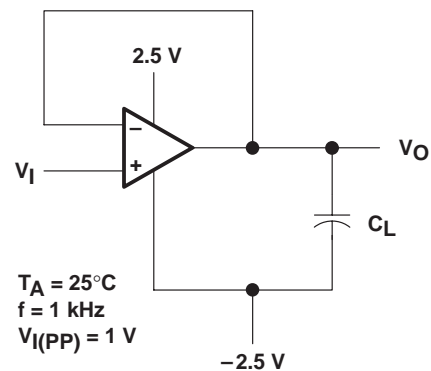
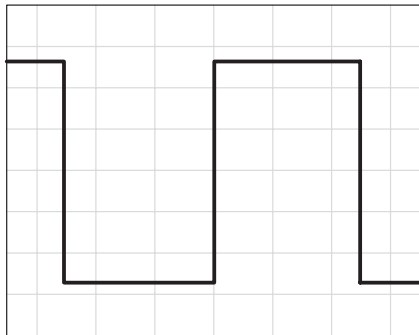


Figure 44. Test Circuit for Output Characteristics

All operating characteristics of the TLV233x are measured using a 20-pF load. The device drives higher capacitive loads; however, as output load capacitance increases, the resulting response pole occurs at lower frequencies thereby causing ringing, peaking, or even oscillation (see Figure 44 and Figure 45). In many cases, adding some compensation in the form of a series resistor in the feedback loop alleviates the problem.

APPLICATION INFORMATION

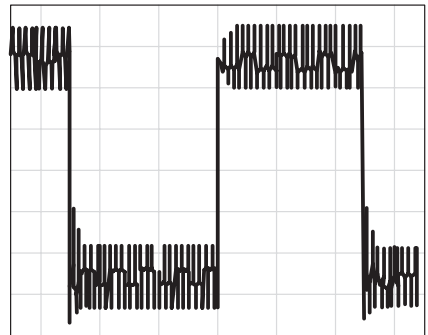
output characteristics (continued)



(a)  $C_L = 20 \text{ pF}$ ,  $R_L = \text{NO LOAD}$



(b)  $C_L = 170 \text{ pF}$ ,  $R_L = \text{NO LOAD}$



(c)  $C_L = 190 \text{ pF}$ ,  $R_L = \text{NO LOAD}$

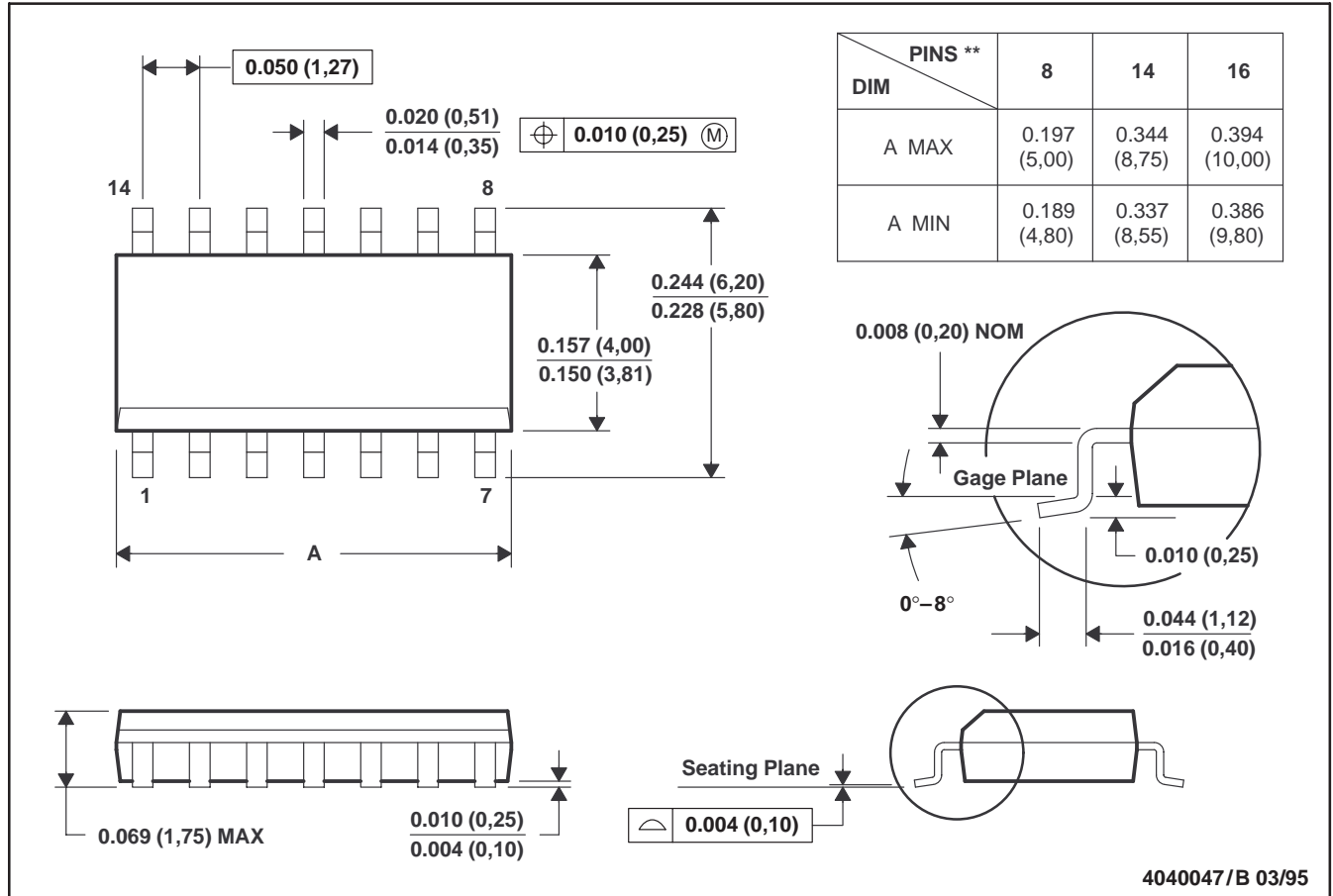
Figure 45. Effect of Capacitive Loads

MECHANICAL INFORMATION

D (R-PDSO-G\*\*)

PLASTIC SMALL-OUTLINE PACKAGE

14 PIN SHOWN



- NOTES: A. All linear dimensions are in inches (millimeters).  
 B. This drawing is subject to change without notice.  
 C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).  
 D. Four center pins are connected to die mount pad.  
 E. Falls within JEDEC MS-012

TLV2332, TLV2332Y, TLV2334, TLV2334Y  
**LinCMOS™ LOW-VOLTAGE MEDIUM-POWER  
 OPERATIONAL AMPLIFIERS**

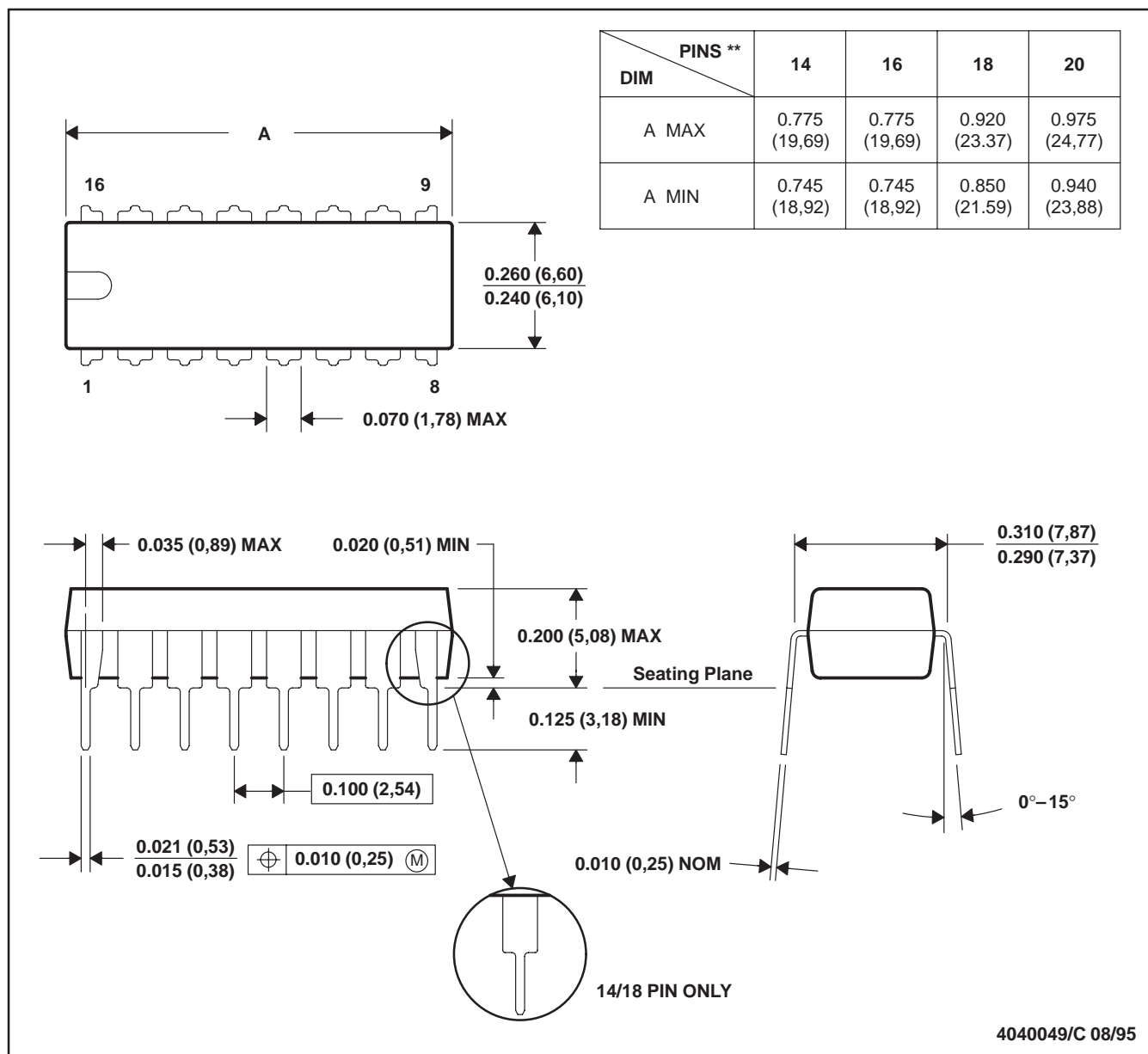
SLOS189 – FEBRUARY 1997

**MECHANICAL INFORMATION**

**N (R-PDIP-T\*\*)**

**PLASTIC DUAL-IN-LINE PACKAGE**

16 PIN SHOWN



- NOTES: A. All linear dimensions are in inches (millimeters).  
 B. This drawing is subject to change without notice.  
 C. Falls within JEDEC MS-001 (20 pin package is shorter than MS-001.)

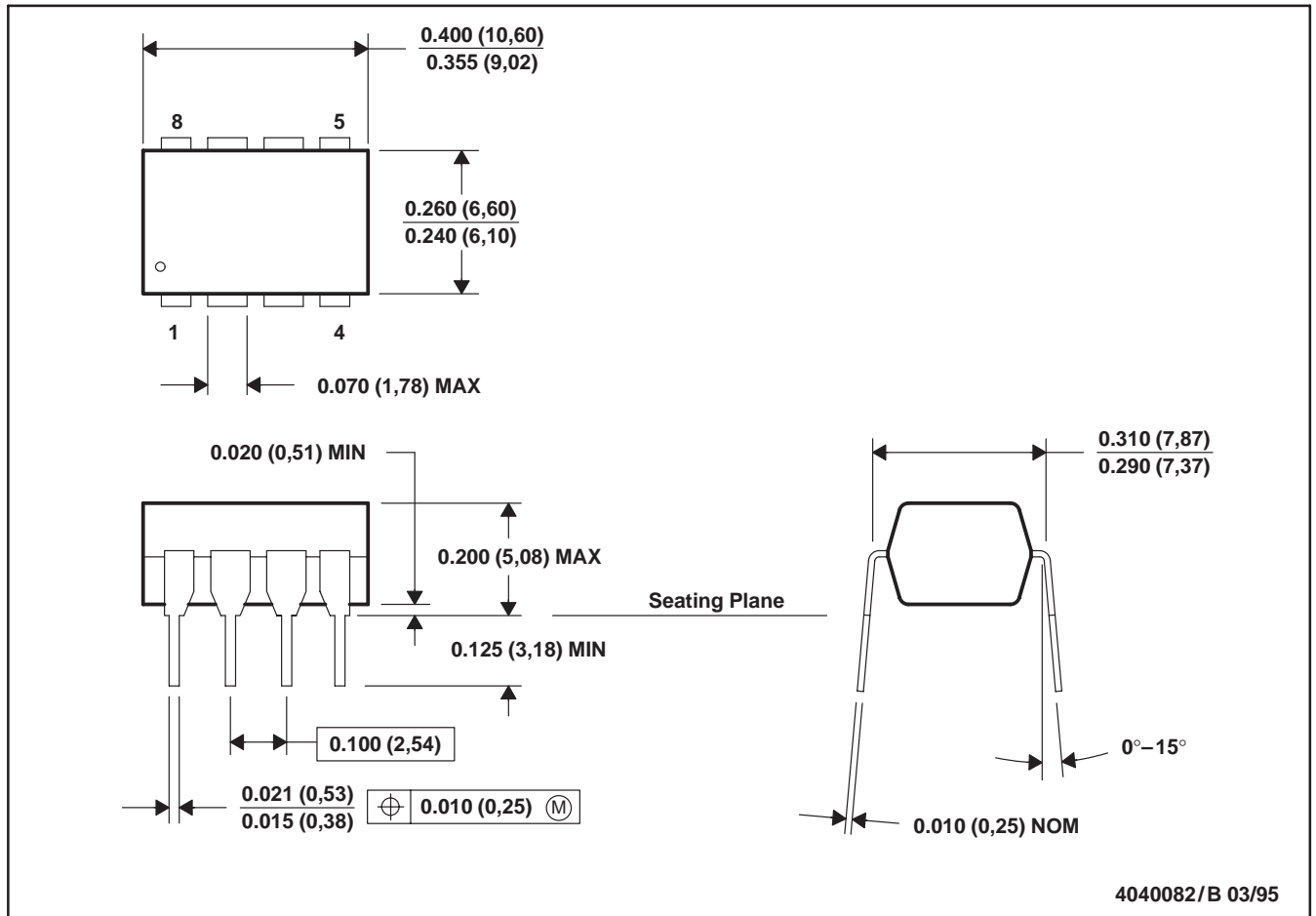


POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

MECHANICAL INFORMATION

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- NOTES: A. All linear dimensions are in inches (millimeters).  
 B. This drawing is subject to change without notice.  
 C. Falls within JEDEC MS-001

**TLV2332, TLV2332Y, TLV2334, TLV2334Y**  
**LinCMOS™ LOW-VOLTAGE MEDIUM-POWER**  
**OPERATIONAL AMPLIFIERS**

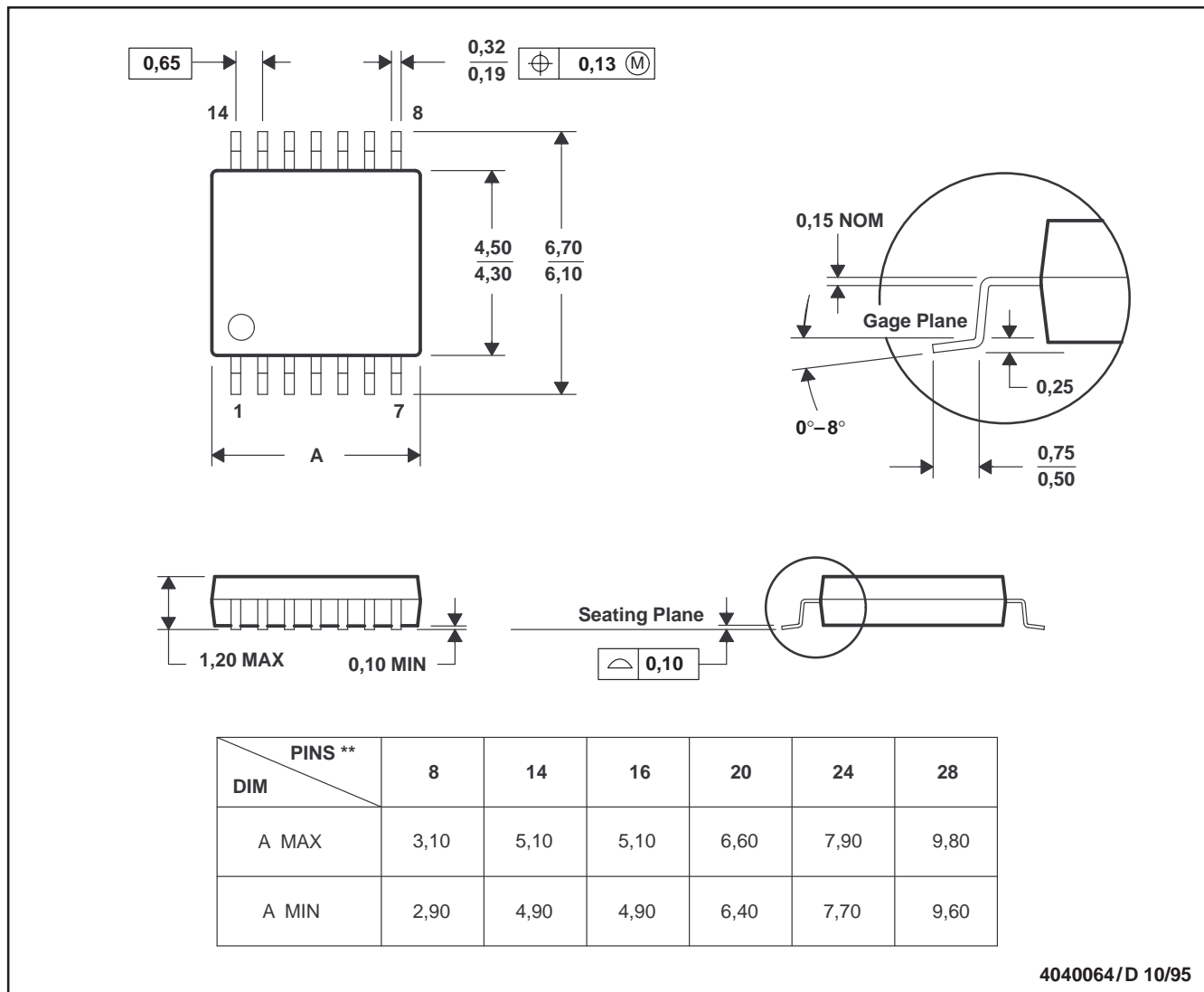
SLOS189 – FEBRUARY 1997

**MECHANICAL INFORMATION**

**PW (R-PDSO-G\*\*)**

**PLASTIC SMALL-OUTLINE PACKAGE**

14 PIN SHOWN



4040064/D 10/95

- NOTES: A. All linear dimensions are in millimeters.  
 B. This drawing is subject to change without notice.  
 C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.  
 D. Falls within JEDEC MO-153



PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
TLV2332ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2332IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2332IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2332IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2332IP	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLV2332IPE4	ACTIVE	PDIP	P	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLV2332IPWLE	OBSOLETE	TSSOP	PW	8		TBD	Call TI	Call TI
TLV2332IPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2332IPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2334ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2334IDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2334IN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLV2334INE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
TLV2334IPWLE	OBSOLETE	TSSOP	PW	14		TBD	Call TI	Call TI
TLV2334IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2334IPWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**TAPE AND REEL INFORMATION**



**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2332IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV2332IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TLV2334IPWR	TSSOP	PW	14	2000	330.0	12.4	7.0	5.6	1.6	8.0	12.0	Q1

**TAPE AND REEL BOX DIMENSIONS**



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2332IDR	SOIC	D	8	2500	340.5	338.1	20.6
TLV2332IPWR	TSSOP	PW	8	2000	346.0	346.0	29.0
TLV2334IPWR	TSSOP	PW	14	2000	346.0	346.0	29.0

## IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

TI products are not authorized for use in safety-critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of TI products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by TI. Further, Buyers must fully indemnify TI and its representatives against any damages arising out of the use of TI products in such safety-critical applications.

TI products are neither designed nor intended for use in military/aerospace applications or environments unless the TI products are specifically designated by TI as military-grade or "enhanced plastic." Only products designated by TI as military-grade meet military specifications. Buyers acknowledge and agree that any such use of TI products which TI has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI products are neither designed nor intended for use in automotive applications or environments unless the specific TI products are designated by TI as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, TI will not be responsible for any failure to meet such requirements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

### Products

Amplifiers	<a href="http://amplifier.ti.com">amplifier.ti.com</a>
Data Converters	<a href="http://dataconverter.ti.com">dataconverter.ti.com</a>
DSP	<a href="http://dsp.ti.com">dsp.ti.com</a>
Clocks and Timers	<a href="http://www.ti.com/clocks">www.ti.com/clocks</a>
Interface	<a href="http://interface.ti.com">interface.ti.com</a>
Logic	<a href="http://logic.ti.com">logic.ti.com</a>
Power Mgmt	<a href="http://power.ti.com">power.ti.com</a>
Microcontrollers	<a href="http://microcontroller.ti.com">microcontroller.ti.com</a>
RFID	<a href="http://www.ti-rfid.com">www.ti-rfid.com</a>
RF/IF and ZigBee® Solutions	<a href="http://www.ti.com/lprf">www.ti.com/lprf</a>

### Applications

Audio	<a href="http://www.ti.com/audio">www.ti.com/audio</a>
Automotive	<a href="http://www.ti.com/automotive">www.ti.com/automotive</a>
Broadband	<a href="http://www.ti.com/broadband">www.ti.com/broadband</a>
Digital Control	<a href="http://www.ti.com/digitalcontrol">www.ti.com/digitalcontrol</a>
Medical	<a href="http://www.ti.com/medical">www.ti.com/medical</a>
Military	<a href="http://www.ti.com/military">www.ti.com/military</a>
Optical Networking	<a href="http://www.ti.com/opticalnetwork">www.ti.com/opticalnetwork</a>
Security	<a href="http://www.ti.com/security">www.ti.com/security</a>
Telephony	<a href="http://www.ti.com/telephony">www.ti.com/telephony</a>
Video & Imaging	<a href="http://www.ti.com/video">www.ti.com/video</a>
Wireless	<a href="http://www.ti.com/wireless">www.ti.com/wireless</a>

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265  
Copyright © 2008, Texas Instruments Incorporated